

GD25LQ256C

DATASHEET



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1. FEATURES

- 256M-bit Serial Flash
 -32768K-byte
 -256 bytes per programmable page
- Standard, Dual, Quad SPI, QPI
 Standard SPI: SCLK, CS#, SI, SO, WP#, HOLD#
 Dual SPI: SCLK, CS#, IO0, IO1, WP#, HOLD#
 Quad SPI: SCLK, CS#, IO0, IO1, IO2, IO3
 QPI: SCLK, CS#, IO0, IO1, IO2, IO3
- High Speed Clock Frequency
 -120MHz for fast read with 30PF load
 -Dual I/O Data transfer up to 240Mbits/s
 -Quad I/O Data transfer up to 480Mbits/s
 -QPI Mode Data transfer up to 480Mbits/s
 -Continuous Read With 8/16/32/64-byte Wrap
- Software/Hardware Write Protection
 -Write protect all/portion of memory via software
 -Enable/Disable protection with WP# Pin
 -Top or Bottom, Sector or Block selection
- Minimum 100,000 Program/Erase Cycles

Note: 1.Please contact GigaDevice for details.

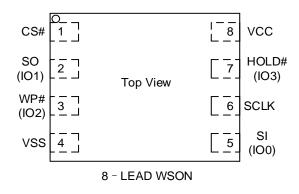
- Program/Erase Speed
 Page Program time: 0.7ms typical
 Sector Erase time: 90ms typical
 Block Erase time: 0.3/0.5s typical
 Chip Erase time: 200s typical
- Flexible Architecture
 -Sector of 4K-byte
 -Block of 32/64k-byte
 -Erase/Program Suspend/Resume
- Low Power Consumption
 -20mA maximum active current
 -10uA maximum power down current
- Advanced security Features
 -128-Bit Unique ID for each device⁽¹⁾
 -2*512-Byte Security Registers With OTP Lock
- Single Power Supply Voltage
 Full voltage range:1.65~2.0V



2. GENERAL DESCRIPTION

The GD25LQ256C (256M-bit) Serial flash supports the standard Serial Peripheral Interface (SPI), and supports the Dual/Quad SPI and QPI mode: Serial Clock, Chip Select, Serial Data I/O0 (SI), I/O1 (SO), I/O2 (WP#), and I/O3 (HOLD#). The Dual I/O data is transferred with speed of 240Mbits/s and the Quad I/O & Quad output data is transferred with speed of 480Mbits/s.

CONNECTION DIAGRAM

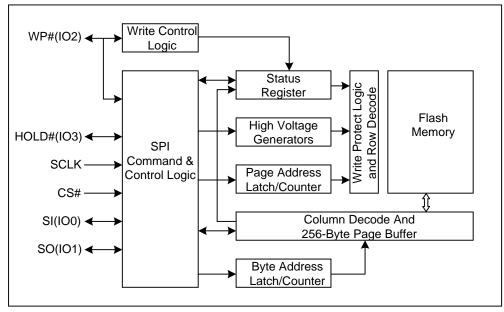


PIN DESCRIPTION

Pin Name	I/O	Description		
CS# I		Chip Select Input		
SO (IO1) I/O		Data Output (Data Input Output 1)		
WP# (IO2) I/O		Write Protect Input (Data Input Output 2)		
VSS		Ground		
SI (IO0)	I/O	Data Input (Data Input Output 0)		
SCLK	I	Serial Clock Input		
HOLD# (IO3)	I/O	Hold Input (Data Input Output 3)		
VCC		Power Supply		

Note: CS# must be driven high if chip is not selected. Please don't leave CS# floating any time after power is on.

BLOCK DIAGRAM





3. MEMORY ORGANIZATION

GD25LQ256C

Each device has	Each block has	Each sector has	Each page has	
32M	64/32K	4K	256	bytes
128K	256/128	16	-	pages
8192	16/8	-	-	sectors
512/1024	-	-	-	blocks

UNIFORM BLOCK SECTOR ARCHITECTURE GD25LQ256C 64K Bytes Block Sector Architecture

Block	Sector	Address range			
	8191	1FFF000H	1FFFFFH		
511					
	8176	1FF0000H	1FF0FFFH		
	8175	1FEF000H	1FEFFFFH		
510					
	8160	1FE0000H	1FE0FFFH		
	47	02F000H	02FFFFH		
2					
	32	020000H	020FFFH		
	31	01F000H	01FFFFH		
1					
	16	010000H	010FFFH		
	15	00F000H	00FFFFH		
0					
	0	000000H	000FFFH		

4. DEVICE OPERATION

SPI Mode

Standard SPI

The GD25LQ256C features a serial peripheral interface on 4 signals bus: Serial Clock (SCLK), Chip Select (CS#), Serial Data Input (SI) and Serial Data Output (SO). Both SPI bus mode 0 and 3 are supported. Input data is latched on the rising edge of SCLK and data shifts out on the falling edge of SCLK.

Dual SPI

The GD25LQ256C supports Dual SPI operation when using the "Dual Output Fast Read" and "Dual I/O Fast Read" (3BH and BBH) commands. These commands allow data to be transferred to or from the device at two times the rate of the standard SPI. When using the Dual SPI command the SI and SO pins become bidirectional I/O pins: IO0 and IO1. **Quad SPI**

The GD25LQ256C supports Quad SPI operation when using the "Quad Output Fast Read", "Quad I/O Fast Read", "Quad Page Program" (6BH, EBH, E7H, 32H) commands. These commands allow data to be transferred to or from the device at four times the rate of the standard SPI. When using the Quad SPI command the SI and SO pins become bidirectional I/O pins: IO0 and IO1, and WP# and HOLD# pins become IO2 and IO3. Quad SPI commands require the non-volatile Quad Enable bit (QE) in Status Register to be set.

QPI

The GD25LQ256C supports Quad Peripheral Interface (QPI) operations only when the device is switched from Standard/Dual/Quad SPI mode to QPI mode using the "Enable the QPI (38H)" command. The QPI mode utilizes all four IO pins to input the command code. Standard/Dual/Quad SPI mode and QPI mode are exclusive. Only one mode can be active at any given times. "Enable the QPI (38H)" and "Disable the QPI (FFH)" commands are used to switch between these two modes. Upon power-up and after software reset using ""Reset (99H)" command, the default state of the device is Standard/Dual/Quad SPI mode requires the non-volatile Quad Enable bit (QE) in Status Register to be set. **Hold**

The HOLD# signal goes low to stop any serial communications with the device, but doesn't stop the operation of write status register, programming, or erasing in progress.

The operation of HOLD, need CS# keep low, and starts on falling edge of the HOLD# signal, with SCLK signal being low (if SCLK is not being low, HOLD operation will not start until SCLK being low). The HOLD condition ends on rising edge of HOLD# signal with SCLK being low (If SCLK is not being low, HOLD operation will not end until SCLK being low).

The SO is high impedance, both SI and SCLK don't care during the HOLD operation, if CS# drives high during HOLD operation, it will reset the internal logic of the device. To re-start communication with chip, the HOLD# must be at high and then CS# must be at low.

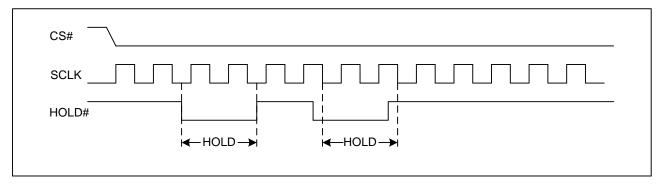


Figure1. Hold Condition

5. DATA PROTECTION

The GD25LQ256C provide the following data protection methods:

- Write Enable (WREN) command: The WREN command is set the Write Enable Latch bit (WEL). The WEL bit will
 return to reset by the following situation:
 - -Power-Up
 - -Write Disable (WRDI)
 - -Write Status Register (WRSR)
 - -Page Program (PP)
 - -Sector Erase (SE) / Block Erase (BE) / Chip Erase (CE)
 - -Erase Security Registers / Program Security Registers
- Software Protection Mode: The Block Protect (BP4, BP3, BP2, BP1, and BP0) bits define the section of the memory array that can be read but not change.
- Hardware Protection Mode: WP# going low to protected the BP0~BP4 bits and SRP0~1 bits.
- Deep Power-Down Mode: In Deep Power-Down Mode, all commands are ignored except the Release from Deep Power-Down Mode command.

ę	Status R	egister	Conten	t	Memory Content					
BP4 BP3 BP2 BP1 BP0				BP0	Blocks	Addresses	Density	Portion		
Х	Х	0	0	0	NONE	NE NONE		NONE		
0	0	0	0	1	504 to 511	1F80000H-1FFFFFFH	512KB	Upper 1/64		
0	0	0	1	0	495 to 511	1F00000H-1FFFFFFH	1MB	Upper 1/32		
0	0	0	1	1	479 to 511	1E00000H-1FFFFFH	2MB	Upper 1/16		
0	0	1	0	0	447 to 511	1C00000H-1FFFFFH	4MB	Upper 1/8		
0	0	1	0	1	384 to 511	1800000H-1FFFFFFH	8MB	Upper 1/4		
0	0	1	1	0	256 to 511	1000000H-1FFFFFFH	16MB	Upper 1/2		
0	1	0	0	1	0 to 7	000000H-07FFFFH	512KB	Lower 1/64		
0	1	0	1	0	0 to 15	000000H-0FFFFH	1MB	Lower 1/32		
0	1	0	1	1	0 to 31	000000H-1FFFFH	2MB	Lower 1/16		
0	1	1	0	0	0 to 63	000000H-3FFFFFH	4MB	Lower 1/8		
0	1	1	0	1	0 to 127	000000H-7FFFFH	8MB	Lower 1/4		
0	1	1	1	0	0 to 255	000000H-0FFFFFH	16MB	Lower 1/2		
Х	Х	1	1	1	0 to 511	000000H-1FFFFFFH	32MB	ALL		
1	0	0	0	1	511	1FFF000H-1FFFFFFH	4KB	Top Block		
1	0	0	1	0	511	1FFE000H-1FFFFFFH	8KB	Top Block		
1	0	0	1	1	511	1FFC000H-1FFFFFFH	16KB	Top Block		
1	0	1	0	Х	511	1FF8000H-1FFFFFFH	32KB	Top Block		
1	0	1	1	0	511	1FF8000H-1FFFFFFH	32KB	Top Block		
1	1	0	0	1	0	000000H-000FFFH	4KB	Bottom Block		
1	1	0	1	0	0	000000H-001FFFH	8KB	Bottom Block		
1	1	0	1	1	0	000000H-003FFFH	16KB	Bottom Block		
1	1	1	0	Х	0	000000H-007FFFH	32KB	Bottom Block		

Table1. GD25LQ256C Protected area size (CMP=0)

1.8V Uniform Sector

 GigaDevice
 Dual and Quad Serial Flash
 GD25LQ256C

 1
 1
 1
 0
 0
 000000H-007FFFH
 32KB
 Bottom Block

Table1a. GD25LQ256C Protected area size (CMP=1)										
;	Status R	Register	Conten	t	Memory Content					
BP4	BP3 BP2 BP1 BP0			BP0	Blocks	Addresses	Density	Portion		
Х	Х	0	0	0	0 to 511	000000H-1FFFFFH	ALL	ALL		
0	0	0	0	1	0 to 503	000000H-1F7FFFFH	32256KB	Lower 63/64		
0	0	0	1	0	0 to 494	000000H-1EFFFFFH	31MB	Lower 31/32		
0	0	0	1	1	0 to 478	000000H-1DFFFFFH	30MB	Lower 15/16		
0	0	1	0	0	0 to 446	000000H-1BFFFFFH	28MB	Lower 7/8		
0	0	1	0	1	0 to 383	000000H-17FFFFFH	24MB	Lower 3/4		
0	0	1	1	0	0 to 254	000000H-0FFFFFH	16MB	Lower 1/2		
0	1	0	0	1	8 to 511	080000H-1FFFFFFH	32256KB	Upper 63/64		
0	1	0	1	0	16 to 511	100000H-1FFFFFFH	31MB	Upper 31/32		
0	1	0	1	1	32 to 511	32 to 511 200000H-1FFFFFH		Upper 15/16		
0	1	1	0	0	64 to 511	400000H-1FFFFFFH	28MB	Upper 7/8		
0	1	1	0	1	128 to 511	800000H-1FFFFFH	24MB	Upper 3/4		
0	1	1	1	0	256 to 511	1000000H-1FFFFFFH	16MB	Upper 1/2		
Х	Х	1	1	1	NONE	NONE	NONE	NONE		
1	0	0	0	1	0 to 511	000000H-1FFEFFFH	32764KB	L-4095/4096		
1	0	0	1	0	0 to 511	000000H-1FFDFFFH	32760KB	L-2047/2048		
1	0	0	1	1	0 to 511	000000H-1FFBFFFH	32752KB	L-1023/1024		
1	0	1	0	Х	0 to 511	000000H-1FF7FFFH	32736KB	L-511/512		
1	0	1	1	0	0 to 511	000000H-1FF7FFFH	32736KB	L-511/512		
1	1	0	0	1	0 to 511	001000H-1FFFFFFH	32764KB	U-4095/4096		
1	1	0	1	0	0 to 511	002000H-1FFFFFFH	32760KB	U-2047/2048		
1	1	0	1	1	0 to 511	004000H-1FFFFFFH	32752KB	U-1023/1024		
1	1	1	0	Х	0 to 511	008000H-1FFFFFFH	32736KB	U-511/512		
1	1	1	1	0	0 to 511	008000H-1FFFFFH	32736KB	U-511/512		

6. Status Register

S15	S14	S13	S12	S11	S10	S9	S8
SUS1	СМР	LB3	LB2	EN4B	SUS2	QE	SRP1
S7	S6	S5	S4	S3	S2	S1	S0
SRP0	BP4	BP3	BP2	BP1	BP0	WEL	WIP

The status and control bits of the Status Register are as follows: **WIP bit.**

The Write in Progress (WIP) bit indicates whether the memory is busy in program/erase/write status register progress. When WIP bit sets to 1, means the device is busy in program/erase/write status register progress, when WIP bit sets 0, means the device is not in program/erase/write status register progress.

WEL bit.

The Write Enable Latch (WEL) bit indicates the status of the internal Write Enable Latch. When set to 1 the internal Write Enable Latch is set, when set to 0 the internal Write Enable Latch is reset and no Write Status Register, Program or Erase command is accepted.

BP4, BP3, BP2, BP1, BP0 bits.

The Block Protect (BP4, BP3, BP2, BP1, and BP0) bits are non-volatile. They define the size of the area to be software protected against Program and Erase commands. These bits are written with the Write Status Register (WRSR) command. When the Block Protect (BP4, BP3, BP2, BP1, BP0) bits are set to 1, the relevant memory area (as defined in Table1).becomes protected against Page Program (PP), Sector Erase (SE) and Block Erase (BE) commands. The Block Protect (BP4, BP3, BP2, BP1, and BP0) bits can be written provided that the Hardware Protected mode has not been set. The Chip Erase (CE) command is executed, if the Block Protect (BP2, BP1, BP0) bits and CMP are all 0 or all 1.

SRP1, SRP0 bits.

The Status Register Protect (SRP1 and SRP0) bits are non-volatile Read/Write bits in the status register. The SRP bits control the method of write protection: software protection, hardware protection, power supply lock-down or one time programmable protection.

SRP1	SRP0	#WP	Status Register	Description
0	0	х	Software Protected	The Status Register can be written to after a Write Enable command, WEL=1.(Default)
0	1	0	Hardware Protected	WP#=0, the Status Register locked and can not be written to.
0	1	1	Hardware Unprotected	WP#=1, the Status Register is unlocked and can be written to after a Write Enable command, WEL=1.
1	0	х	Power Supply Lock-Down ⁽¹⁾⁽²⁾	Status Register is protected and can not be written to again until the next Power-Down, Power-Up cycle.
1	1	х	One Time Program ⁽²⁾	Status Register is permanently protected and can not be written to.

NOTE:

1. When SRP1, SRP0= (1, 0), a Power-Down, Power-Up cycle will change SRP1, SRP0 to (0, 0) state.

2. This feature is available on special order. Please contact GigaDevice for details.



QE bit.

The Quad Enable (QE) bit is a non-volatile Read/Write bit in the Status Register that allows Quad operation. When the QE bit is set to 0 (Default) the WP# pin and HOLD# pin are enable. When the QE pin is set to 1, the Quad IO2 and IO3 pins are enabled. (It is best to set the QE bit to 0 to avoid short issue if the WP# or HOLD# pin is tied directly to the power supply or ground.)

LB2, LB3, bits.

The LB2, LB3, bits are non-volatile One Time Program (OTP) bits in Status Register (S12-S13) that provide the write protect control and status to the Security Registers. The default state of LB2-LB3 are 0, the security registers are unlocked. The LB2-LB3 bits can be set to 1 individually using the Write Register instruction. The LB2-LB3 bits are One Time Programmable, once its set to 1, the Security Registers will become read-only permanently.

CMP bit

The CMP bit is a non-volatile Read/Write bit in the Status Register (S14). It is used in conjunction the BP4-BP0 bits to provide more flexibility for the array protection. Please see the Status registers Memory Protection table for details. The default setting is CMP=0.

SUS1, SUS2 bit

The SUS1 and SUS2 bit are read only bit in the status register (S15 and S10) that are set to 1 after executing an Erase/Program Suspend (75H) command (The Erase Suspend will set the SUS1 to 1, and the Program Suspend will set the SUS2 to 1). The SUS1 and SUS2 bit are cleared to 0 by Erase/Program Resume (7AH) command as well as a power-down, power-up cycle.

EN4B bit

The EN4B bit is a volatile read only bit in the status register (S11) that is set to 1 after executing the Enable 4-byte Mode command, and cleared to 0 (default) by the Disable 4-byte Mode command as well as a power-down, power-up cycle.

7. COMMANDS DESCRIPTION

All commands, addresses and data are shifted in and out of the device, beginning with the most significant bit on the first rising edge of SCLK after CS# is driven low. Then, the one-byte command code must be shifted in to the device, most significant bit first on SI, each bit being latched on the rising edges of SCLK.

See Table2, every command sequence starts with a one-byte command code. Depending on the command, this might be followed by address bytes, or by data bytes, or by both or none. CS# must be driven high after the last bit of the command sequence has been shifted in. For the command of Read, Fast Read, Read Status Register or Release from Deep Power-Down, and Read Device ID, the shifted-in command sequence is followed by a data-out sequence. All read instruction can be completed after any bit of the data-out sequence is being shifted out, and then CS# must be driven high to return to deselected status.

For the command of Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register, Write Enable, Write Disable or Deep Power-Down command, CS# must be driven high exactly at a byte boundary, otherwise the command is rejected, and is not executed. That is CS# must driven high when the number of clock pulses after CS# being driven low is an exact multiple of eight. For Page Program, if at any time the input byte is not a full byte, nothing will happen and WEL will not be reset.

Command Name	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6	n-Bytes
Write Enable	06H						
Write Disable	04H						
Volatile SR	50H						
Write Enable							
Read Status Register	05H	(S7-S0)					(continuous)
Read Status Register-1	35H	(S15-S8)					(continuous)
Write Status Register	01H	(S7-S0)	(S15-S8)				
Read Data	03H	A23-A16	A15-A8	A7-A0	(D7-D0)	(Next byte)	(continuous)
Fast Read	0BH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)	(continuous)
Dual Output Fast Read	3BH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0) ⁽¹⁾	(continuous)
Dual I/O Fast Read	BBH	A23-A8 ⁽²⁾	A7-A0 M7-M0 ⁽²⁾	(D7-D0) ⁽¹⁾			(continuous)
Quad Output Fast Read	6BH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0) ⁽³⁾	(continuous)
Quad I/O Fast Read	EBH	A23-A0 M7-M0 ⁽⁴⁾	dummy ⁽⁵⁾	(D7-D0) ⁽³⁾			(continuous)
Quad I/O Word Fast Read ⁽⁷⁾	E7H	A23-A0 M7-M0 ⁽⁴⁾	dummy ⁽⁶⁾	(D7-D0) ⁽³⁾			(continuous)
Page Program	02H	A23-A16	A15-A8	A7-A0	(D7-D0)	Next byte	
Quad Page Program	32H	A23-A16	A15-A8	A7-A0	(D7-D0) ⁽³⁾		
Sector Erase	20H	A23-A16	A15-A8	A7-A0			
Block Erase(32K)	52H	A23-A16	A15-A8	A7-A0			
Block Erase(64K)	D8H	A23-A16	A15-A8	A7-A0			
Chip Erase	C7/60H						
Enable QPI	38H						
Enable Reset	66H						
Reset	99H						
Set Burst with Wrap	77H	W6-W4					
Program/Erase Suspend	75H						
Program/Erase Resume	7AH						

Table2. Commands (Standard/Dual/Quad SPI) (3-byte mode)



1.8V Uniform Sector Dual and Quad Serial Flash

GD25LQ256C

Release From Deep	ABH	dummy	dummy	dummy	(ID7-ID0)		(continuous)
Power-Down, And							
Read Device ID							
Release From Deep	ABH						
Power-Down		_					
Deep Power-Down	B9H						
Manufacturer/	90H	dummy	dummy	00H	(M7-M0)	(ID7-ID0)	(continuous)
Device ID							
Manufacturer/	0011	100.10	A7-A0,	(M7-M0)			(
Device ID by Dual I/O	92H	A23-A8	M[7:0]	(ID7-ID0)			(continuous)
Manufacturer/	0.411	A23-A0,	dummy	(M7-M0)			
Device ID by Quad I/O	94H	M[7:0]		(ID7-ID0)			(continuous)
Read Identification	9FH	(M7-M0)	(ID15-ID8)	(ID7-ID0)			(continuous)
Read Serial Flash	5AH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)	(continuous)
Discoverable							
Parameter ⁽¹⁰⁾							
Erase Security	44H	A23-A16	A15-A8	A7-A0			
Registers ⁽⁸⁾							
Program Security	42H	A23-A16	A15-A8	A7-A0	(D7-D0)	(D7-D0)	
Registers ⁽⁸⁾					, ,	, ,	
Read Security	48H	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)	
Registers ⁽⁸⁾							
Enable 4-byte Mode	B7H						
Disable 4-byte Mode	E9H						

Table2.1. Commands (Standard/Dual/Quad SPI) (4-byte mode)

			=	-		-	
Command Name	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6	Byte 7
Read Data	03H	A31-A24	A23-A16	A15-A8	A7-A0	(D7-D0)	(Next byte)
Fast Read	0BH	A31-A24	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Dual Output Fast Read	3BH	A31-A24	A23-A16	A15-A8	A7-A0	dummy	(D7-D0) ⁽¹⁾
Dual I/O Fast Read	BBH	A31-A24	A23-A8 ⁽²⁾	A7-A0 M7-M0 ⁽²⁾	(D7-D0) ⁽¹⁾		
Quad Output Fast Read	6BH	A31-A24	A23-A16	A15-A8	A7-A0	dummy	(D7-D0) ⁽³⁾
Quad I/O Fast Read	EBH	A31-A0	M7-M0 ⁽⁴⁾	dummy ⁽⁵⁾	(D7-D0) ⁽³⁾		
Quad I/O Word Fast Read ⁽⁷⁾	E7H	A31-A0	M7-M0 ⁽⁴⁾	dummy ⁽⁶⁾	(D7-D0) ⁽³⁾		
Page Program	02H	A31-A24	A23-A16	A15-A8	A7-A0	(D7-D0)	Next byte
Quad Page Program	32H	A31-A24	A23-A16	A15-A8	A7-A0	(D7-D0) ⁽³⁾	
Sector Erase	20H	A31-A24	A23-A16	A15-A8	A7-A0		
Block Erase(32K)	52H	A31-A24	A23-A16	A15-A8	A7-A0		
Block Erase(64K)	D8H	A31-A24	A23-A16	A15-A8	A7-A0		



Table2a. Commands	(QPI) (3-byte mode)
-------------------	---------------------

Command Name	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6
Clock Number	(0,1)	(2,3)	(4,5)	(6,7)	(8,9)	(10,11)
Write Enable	06H					
Volatile SR Write Enable	50H					
Write Disable	04H					
Read Status Register	05H	(S7-S0)				
Read Status Register-1	35H	(S15-S8)				
Read Status Register-2	15H	(S1-S0)				
Write Status Register	01H	(S7-S0)	(S15-S8)			
Page Program	02H	A23-A16	A15-A8	A7-A0	(D7-D0)	Next byte
Sector Erase	20H	A23-A16	A15-A8	A7-A0		
Block Erase(32K)	52H	A23-A16	A15-A8	A7-A0		
Block Erase(64K)	D8H	A23-A16	A15-A8	A7-A0		
Chip Erase	C7/60H					
Program/Erase Suspend	75H					
Program/Erase Resume	7AH					
Deep Power-Down	B9H					
Set Read Parameters	COH	P7-P0				
Fast Read	0BH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Burst Read with Wrap	0CH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Burst Read with Wrap for Lower 128Mb (A24=0)	8CH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Burst Read with Wrap for Higher 128Mb (A24=1)	8DH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Quad I/O Fast Read	EBH	A23-A16	A15-A8	A7-A0	M7-M0	(D7-D0)
Release From Deep Power-Down, And Read Device ID	ABH	dummy	dummy	dummy	(ID7-ID0)	
Manufacturer/ Device ID	90H	dummy	dummy	00H	(M7-M0)	(ID7-ID0)
Read Identification	9FH	(M7-M0)	(ID15-ID8)	(ID7-ID0)		
Read Serial Flash Discoverable Parameter ⁽¹⁰⁾	5AH	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Disable QPI	FFH					
Enable Reset	66H					
Reset	99H					
Enable 4-byte Mode	B7H					
Disable 4-byte Mode	E9H					

Command Name	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6	Byte7
Clock Number	(0,1)	(2,3)	(4,5)	(6,7)	(8,9)	(10,11)	(12,13)
Page Program	02H	A31-A24	A23-A16	A15-A8	A7-A0	(D7-D0)	Next byte
Sector Erase	20H	A31-A24	A23-A16	A15-A8	A7-A0		
Block Erase(32K)	52H	A31-A24	A23-A16	A15-A8	A7-A0		
Block Erase(64K)	D8H	A31-A24	A23-A16	A15-A8	A7-A0		
Fast Read	0BH	A31-A24	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Burst Read with Wrap	0CH	A31-A24	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Quad I/O Fast Read	EBH	A31-A24	A23-A16	A15-A8	A7-A0	M7-M0	(D7-D0)



NOTE:	
1. Dual Output data	
IO0 = (D6, D4, D2, D0)	
IO1 = (D7, D5, D3, D1)	
2. Dual Input Address	
IO0 = A22, A20, A18, A16, A14, A12, A10, A8	A6, A4, A2, A0, M6, M4, M2, M0
IO1 = A23, A21, A19, A17, A15, A13, A11, A9	A7, A5, A3, A1, M7, M5, M3, M1
3. Quad Output Data	
IO0 = (D4, D0,)	
IO1 = (D5, D1,)	
IO2 = (D6, D2,)	
IO3 = (D7, D3,)	
4. Quad Input Address	
IO0 = A20, A16, A12, A8, A4, A0, M4, M0	
IO1 = A21, A17, A13, A9, A5, A1, M5, M1	
IO2 = A22, A18, A14, A10, A6, A2, M6, M2	
IO3 = A23, A19, A15, A11, A7, A3, M7, M3	
5. Fast Read Quad I/O Data	
IO0 = (x, x, x, x, D4, D0,)	
IO1 = (x, x, x, x, D5, D1,)	
IO2 = (x, x, x, x, D6, D2,)	
IO3 = (x, x, x, x, D7, D3,)	
6. Fast Word Read Quad I/O Data	
IO0 = (x, x, D4, D0,)	
IO1 = (x, x, D5, D1,)	
IO2 = (x, x, D6, D2,)	
IO3 = (x, x, D7, D3,)	
7. Fast Word Read Quad I/O Data: the lowest address I	bit must be 0.
8. Security Registers Address:	
Security Register2: A23-A16=00H, A15-A9=	=0010000b, A8-A0=Byte Address;
Security Register3: A23-A16=00H, A15-A9=	=0011000b, A8-A0=Byte Address.
9. QPI Command, Address, Data input/output format:	
CLK #0 1 2 3 4 5 6 7	
IO0= C4, C0, A20, A16, A12, A8, A4, A0	
	, D5, D1, D5, D1
IO2= C6, C2, A22, A18, A14, A10, A6, A2	
IO3= C7, C3, A23, A19, A15, A11, A7, A3	s, D7, D3, D7, D3

10. Read Serial Flash Discoverable Parameter (SFDP) command is available on special order. Please contact GigaDevice if this function is needed.



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Table of ID Definitions:

GD25LQ256C

Operation Code	M7-M0	ID15-ID8	ID7-ID0
9FH	C8	60	19
90H	C8		18
ABH			18

7.1. Enable 4-byte Mode (B7H)

The Enable 4-byte Mode command enables accessing the address length of 32-bit for the memory area of the higher density (larger than 128Mb). The GD25LQ256C default is in 24-bit address mode. After sending the Enable 4-byte Mode command, the EN4B bit (S11) will be set to 1 to indicate the 4-byte address mode has been enabled. Once the 4-byte address mode is enabled, the address length becomes 32-bit instead of the default 24 bit. The Disable 4-byte mode or Reset or Power-off will disable 4-byte mode. In the 4-byte mode, A31-A25 are don't care.

Figure2. Enable 4-byte Mode Sequence Diagram

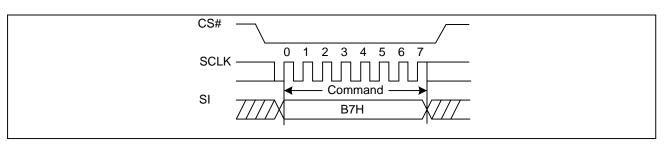
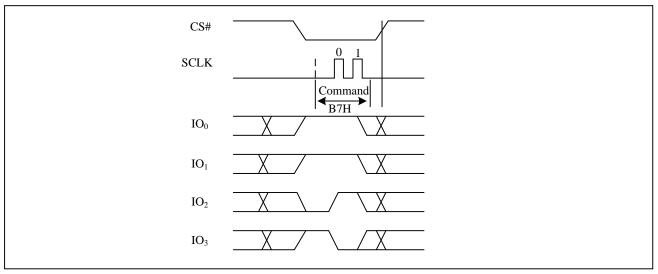


Figure2a. Enable 4-byte Mode Sequence Diagram (QPI)





7.2. Disable 4-byte Mode (E9H)

The Disable 4-byte Mode command is executed to exit the 4-byte address mode and return to the default 3-byte address mode. After sending the Disable 4-byte Mode command, the EN4B bit (S11) will be clear to be 0 to indicate the 4-byte address mode has been disabled, and then the address length will return to 24-bit.



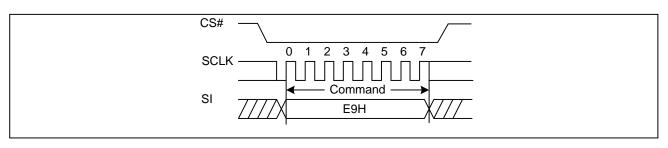
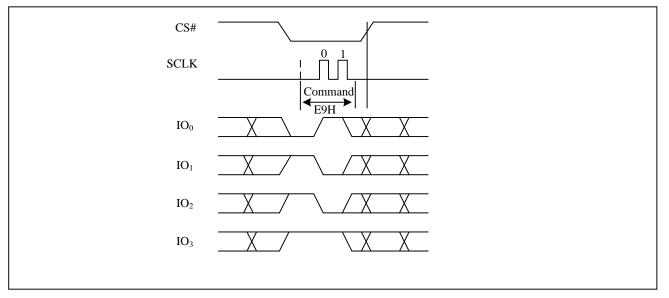


Figure3a. Disable 4-byte Mode Sequence Diagram (QPI)



7.3. Write Enable (WREN) (06H)

The Write Enable (WREN) command is for setting the Write Enable Latch (WEL) bit. The Write Enable Latch (WEL) bit must be set prior to every Page Program (PP), Sector Erase (SE), Block Erase (BE), Chip Erase (CE), Write Status Register (WRSR) and Erase/Program Security Registers command. The Write Enable (WREN) command sequence: CS# goes low \rightarrow sending the Write Enable command \rightarrow CS# goes high.

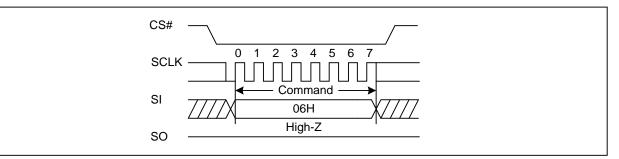
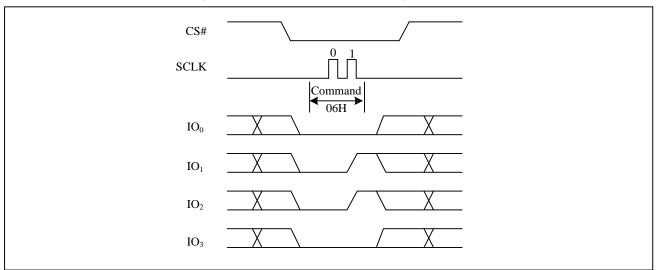


Figure4. Write Enable Sequence Diagram

Figure4a. Write Enable Sequence Diagram (QPI)



7.4. Write Disable (WRDI) (04H)

The Write Disable command is for resetting the Write Enable Latch (WEL) bit. The Write Disable command sequence: CS# goes low \rightarrow Sending the Write Disable command \rightarrow CS# goes high. The WEL bit is reset by following condition: Power-up and upon completion of the Write Status Register, Page Program, Sector Erase, Block Erase, Chip Erase, Erase/Program Security Registers and Reset commands.

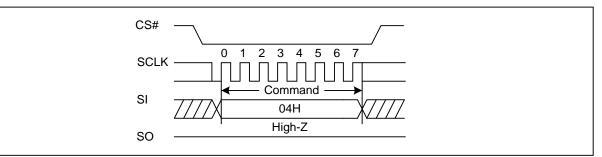
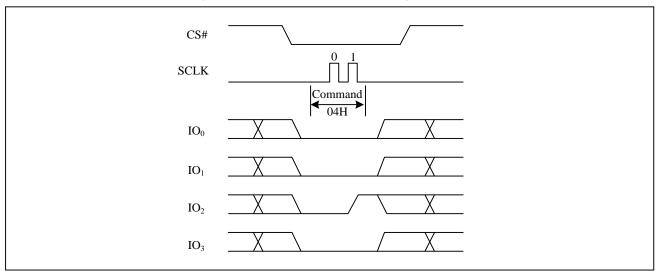


Figure 5. Write Disable Sequence Diagram

Figure5a. Write Disable Sequence Diagram (QPI)



7.5. Write Enable for Volatile Status Register (50H)

The non-volatile Status Register bits can also be written to as volatile bits. This gives more flexibility to change the system configuration and memory protection schemes quickly without waiting for the typical non-volatile bit write cycles or affecting the endurance of the Status Register non-volatile bits. The Write Enable for Volatile Status Register command must be issued prior to a Write Status Register command. The Write Enable for Volatile Status Register command will not set the Write Enable Latch bit, it is only valid for the Write Status Register command to change the volatile Status Register bit values.

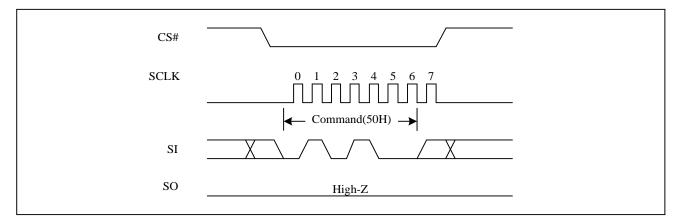
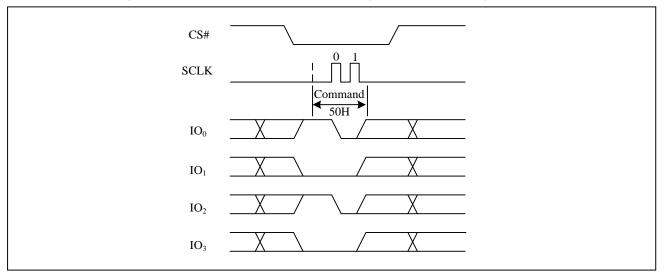


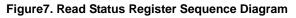
Figure6. Write Enable for Volatile Status Register Sequence Diagram

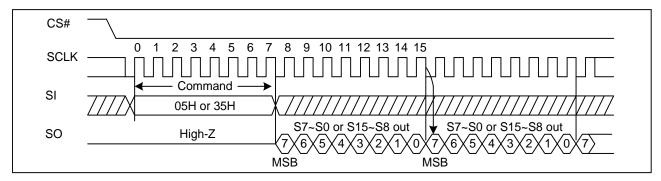
Figure6a. Write Enable for Volatile Status Register Sequence Diagram (QPI)



7.6. Read Status Register (RDSR) (05H or 35H or 15H)

The Read Status Register (RDSR) command is for reading the Status Register. The Status Register may be read at any time, even while a Program, Erase or Write Status Register cycle is in progress. When one of these cycles is in progress, it is recommended to check the Write in Progress (WIP) bit before sending a new command to the device. It is also possible to read the Status Register continuously. For command code "05H" / "35H", the SO will output Status Register bits S7~S0 / S15-S8. The command code "15H" only supports the QPI mode, the I/O0 will output Status Register S1-S0. (For 120MHz Frequency, the 15H will better than 05H to check the WIP bit)







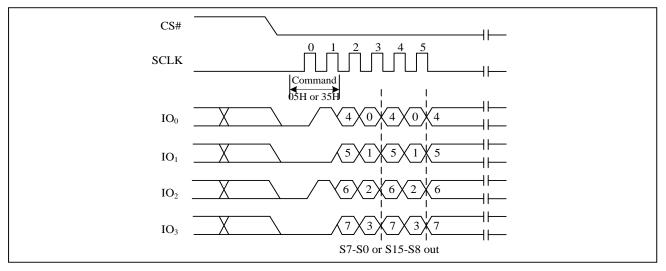
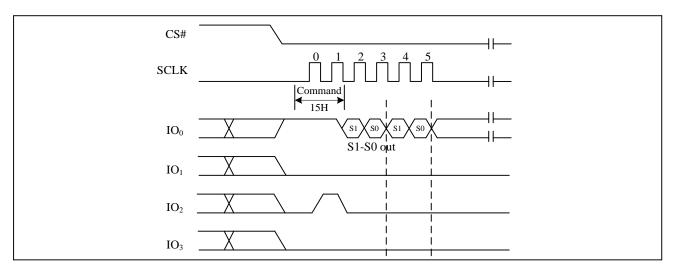


Figure7b. Read Status Register Sequence Diagram (QPI) (15H)



7.7. Write Status Register (WRSR) (01H)

The Write Status Register (WRSR) command allows new values to be written to the Status Register. Before it can be accepted, a Write Enable (WREN) command must previously have been executed. After the Write Enable (WREN) command has been decoded and executed, the device sets the Write Enable Latch (WEL).

The Write Status Register (WRSR) command has no effect on S15, S11, S10, S1 and S0 of the Status Register. CS# must be driven high after the eighth or sixteen bit of the data byte has been latched in. If not, the Write Status Register (WRSR) command is not executed. If CS# is driven high after eighth bit of the data byte, the CMP and QE bits will be cleared to 0 in SPI mode, while only CMP will be cleared to 0 in QPI mode. As soon as CS# is driven high, the self-timed Write Status Register cycle (whose duration is tw) is initiated. While the Write Status Register cycle is in progress, the Status Register may still be read to check the value of the Write In Progress (WIP) bit. The Write In Progress (WIP) bit is 1 during the self-timed Write Status Register cycle, and is 0 when it is completed. When the cycle is completed, the Write Enable Latch (WEL) is reset.

The Write Status Register (WRSR) command allows the user to change the values of the Block Protect (BP4, BP3, BP2, BP1, and BP0) bits, to define the size of the area that is to be treated as read-only, as defined in Table1. The Write Status Register (WRSR) command also allows the user to set or reset the Status Register Protect (SRP1 and SRP0) bits in accordance with the Write Protect (WP#) signal. The Status Register Protect (SRP1 and SRP0) bits and Write Protect (WP#) signal allow the device to be put in the Hardware Protected Mode. The Write Status Register (WRSR) command is not executed once the Hardware Protected Mode is entered.

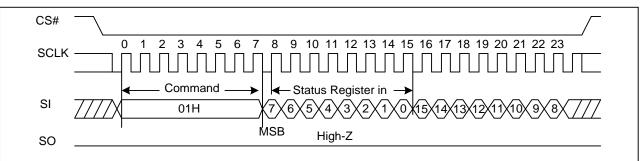
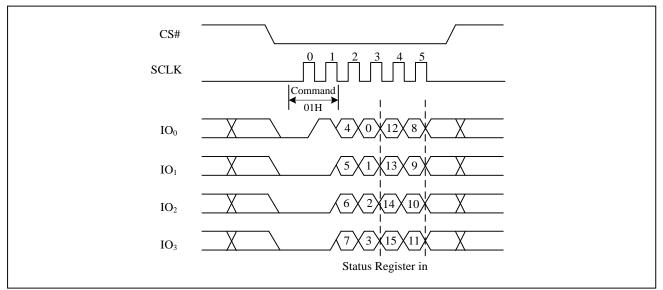


Figure8. Write Status Register Sequence Diagram



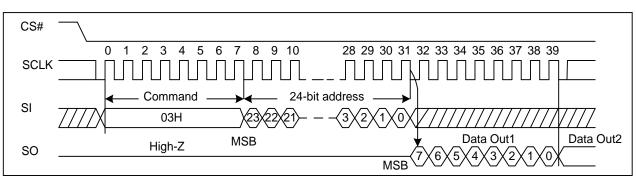
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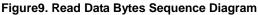
Figure8a. Write Status Register Sequence Diagram (QPI)



7.8. Read Data Bytes (READ) (03H)

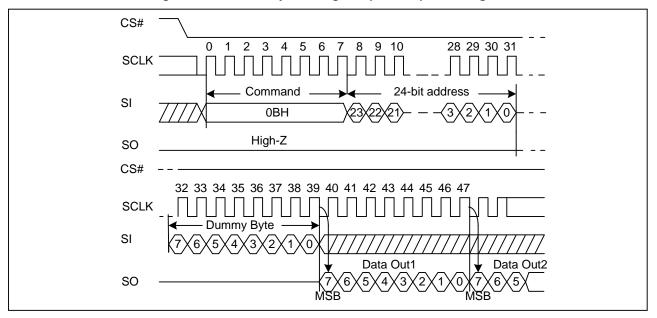
The Read Data Bytes (READ) command is followed by a 3-byte address (A23-A0) or a 4-byte address (A31-A0), each bit being latched-in during the rising edge of SCLK. Then the memory content, at that address, is shifted out on SO, each bit being shifted out, at a Max frequency f_R, during the falling edge of SCLK. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. The default read mode is 3-byte address mode, and the lower 128Mbit can be read with a single Read Data Byte (03H) command. By entering 4-byte address mode, or to set EN4B (S11) bit to 1, the higher 128Mbit can be read with a single Read with a single Read Data Byte (03H) command. Any Read Data Bytes (READ) command, while an Erase, Program or Write cycle is in progress, is rejected without having any effects on the cycle that is in progress.





7.9. Read Data Bytes at Higher Speed (Fast Read) (0BH)

The Read Data Bytes at Higher Speed (Fast Read) command is for quickly reading data out. It is followed by a 3-byte address (A23-A0) or a 4-byte address (A31-A0) and a dummy byte, each bit being latched-in during the rising edge of SCLK. Then the memory content, at that address, is shifted out on SO, each bit being shifted out, at a Max frequency fc, during the falling edge of SCLK. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out.





Fast Read (0BH) in QPI mode

The Fast Read command is also supported in QPI mode. In QPI mode, the number of dummy clocks is configured by the "Set Read Parameters (C0H)" command to accommodate a wide range application with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P[5:4] setting, the number of dummy clocks can be configured as either 4/6/8/8.

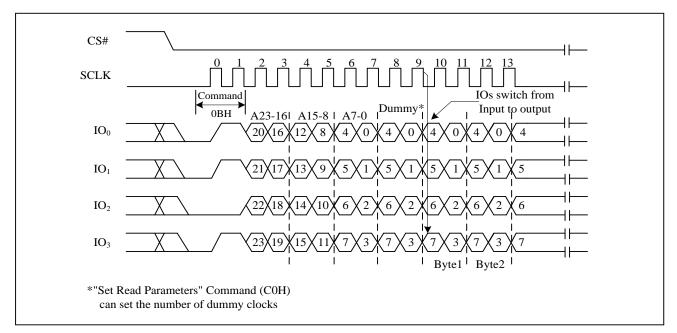


Figure10a. Read Data Bytes at Higher Speed Sequence Diagram (QPI)

Dual Output Fast Read (3BH) 7.10.

The Dual Output Fast Read command is followed by 3-byte address (A23-A0) or a 4-byte address (A31-A0)and a dummy byte, each bit being latched in during the rising edge of SCLK, then the memory contents are shifted out 2-bit per clock cycle from SI and SO. The command sequence is shown in followed Figure 11. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out.

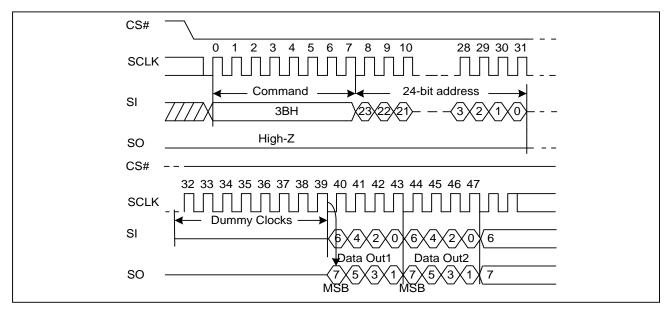


Figure11. Dual Output Fast Read Sequence Diagram

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7.11. Quad Output Fast Read (6BH)

The Quad Output Fast Read command is followed by 3-byte address (A23-A0) or a 4-byte address (A31-A0) and a dummy byte, each bit being latched in during the rising edge of SCLK, then the memory contents are shifted out 4-bit per clock cycle from IO3, IO2, IO1 and IO0. The command sequence is shown in followed Figure 12. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out.

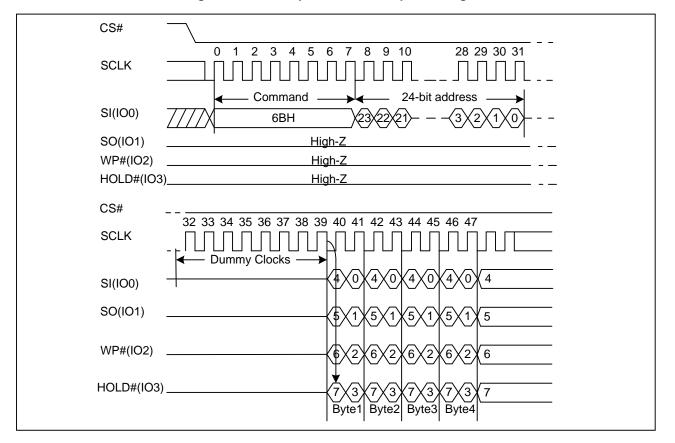


Figure12. Quad Output Fast Read Sequence Diagram

7.12. Dual I/O Fast Read (BBH)

The Dual I/O Fast Read command is similar to the Dual Output Fast Read command but with the capability to input the 3-byte address (A23-0) or a 4-byte address (A31-A0) and a "Continuous Read Mode" byte 2-bit per clock by SI and SO, each bit being latched in during the rising edge of SCLK, then the memory contents are shifted out 2-bit per clock cycle from SI and SO. The command sequence is shown in followed Figure 13. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out.

Dual I/O Fast Read with "Continuous Read Mode"

The Dual I/O Fast Read command can further reduce command overhead through setting the "Continuous Read Mode" bits (M7-0) after the input 3-byte address (A23-A0) or a 4-byte address (A31-A0). If the "Continuous Read Mode" bits (M5-4) = (1, 0), then the next Dual I/O Fast Read command (after CS# is raised and then lowered) does not require the BBH command code. The command sequence is shown in followed Figure 13a. If the "Continuous Read Mode" bits (M5-4) do not equal (1, 0), the next command requires the first BBH command code, thus returning to normal operation. A "Continuous Read Mode" Reset command can be used to reset (M5-4) before issuing normal command.

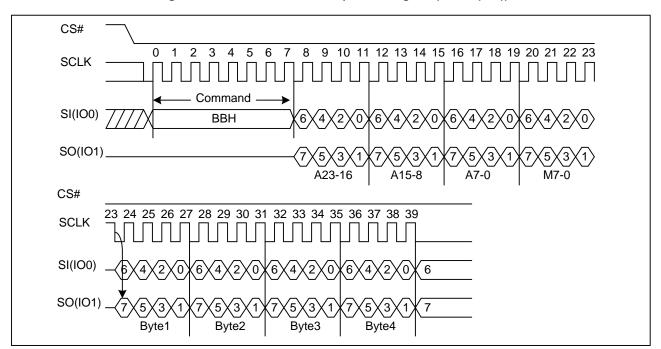
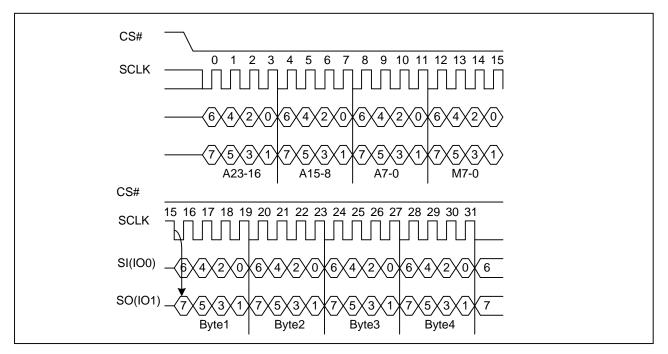


Figure13. Dual I/O Fast Read Sequence Diagram (M5-4≠ (1, 0))

Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.



Figure13a. Dual I/O Fast Read Sequence Diagram (M5-4= (1, 0))



7.13. Quad I/O Fast Read (EBH)

The Quad I/O Fast Read command is similar to the Dual I/O Fast Read command but with the capability to input the 3-byte address (A23-0) or a 4-byte address (A31-A0) and a "Continuous Read Mode" byte and 4-dummy clock 4-bit per clock by IO0, IO1, IO3, IO4, each bit being latched in during the rising edge of SCLK, then the memory contents are shifted out 4-bit per clock cycle from IO0, IO1, IO2, IO3. The command sequence is shown in followed Figure14. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. The Quad Enable bit (QE) of Status Register (S9) must be set to enable for the Quad I/O Fast read command.

Quad I/O Fast Read with "Continuous Read Mode"

The Quad I/O Fast Read command can further reduce command overhead through setting the "Continuous Read Mode" bits (M7-0) after the input 3-byte address (A23-A0) or a 4-byte address (A31-A0). If the "Continuous Read Mode" bits (M5-4) = (1, 0), then the next Quad I/O Fast Read command (after CS# is raised and then lowered) does not require the EBH command code. The command sequence is shown in followed Figure14a. If the "Continuous Read Mode" bits (M5-4) do not equal to (1, 0), the next command requires the first EBH command code, thus returning to normal operation. A "Continuous Read Mode" Reset command can be used to reset (M5-4) before issuing normal command.

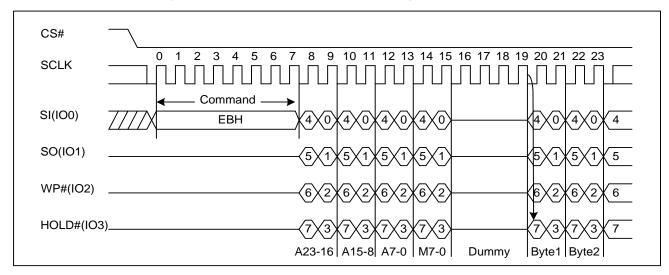
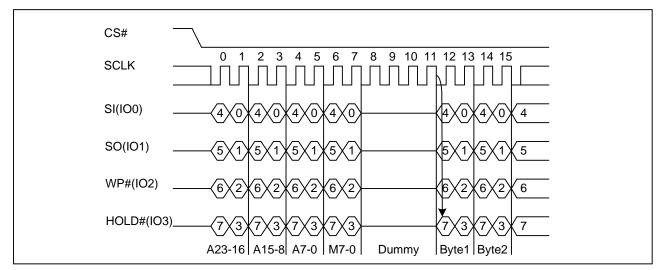


Figure14. Quad I/O Fast Read Sequence Diagram (M5-4≠ (1, 0))



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Figure14a. Quad I/O Fast Read Sequence Diagram (M5-4= (1, 0))



Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.

Quad I/O Fast Read with "8/16/32/64-Byte Wrap Around" in Standard SPI mode

The Quad I/O Fast Read command can be used to access a specific portion within a page by issuing "Set Burst with Wrap" (77H) commands prior to EBH. The "Set Burst with Wrap" (77H) command can either enable or disable the "Wrap Around" feature for the following EBH commands. When "Wrap Around" is enabled, the data being accessed can be limited to either an 8/16/32/64-byte section of a 256-byte page. The output data starts at the initial address specified in the command, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around the beginning boundary automatically until CS# is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing multiple read commands. The "Set Burst with Wrap" command allows three "Wrap Bits" W6-W4 to be set. The W4 bit is used to enable or disable the "Wrap Around" operation while W6-W5 is used to specify the length of the wrap around section within a page.

Quad I/O Fast Read (EBH) in QPI mode

The Quad I/O Fast Read command is also supported in QPI mode. See Figure14b. In QPI mode, the number of dummy clocks is configured by the "Set Read Parameters (C0H)" command to accommodate a wide range application with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P[5:4] setting, the number of dummy clocks can be configured as either 4/6/8/8. In QPI mode, the "Continuous Read Mode" bits M7-M0 are also considered as dummy clocks. "Continuous Read Mode" feature is also available in QPI mode for Quad I/O Fast Read command. "Wrap Around" feature is not available in QPI mode, a dedicated "Burst Read with Wrap" (0CH) command must be used.

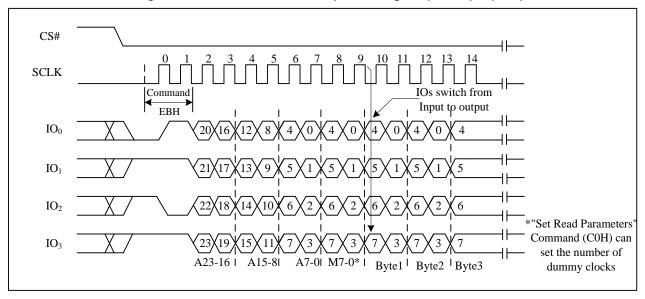


Figure14b. Quad I/O Fast Read Sequence Diagram (M5-4= (1, 0) QPI)

Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.

7.14. Quad I/O Word Fast Read (E7H)

The Quad I/O Word Fast Read command is similar to the Quad I/O Fast Read command except that the lowest address bit (A0) must equal 0 and only 2-dummy clock. The command sequence is shown in followed Figure 15. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. The Quad Enable bit (QE) of Status Register (S9) must be set to enable for the Quad I/O Word Fast read command.

Quad I/O Word Fast Read with "Continuous Read Mode"

The Quad I/O Word Fast Read command can further reduce command overhead through setting the "Continuous Read Mode" bits (M7-0) after the input 3-byte address (A23-A0) or a 4-byte address (A31-A0). If the "Continuous Read Mode" bits (M5-4) = (1, 0), then the next Quad I/O Word Fast Read command (after CS# is raised and then lowered) does not require the E7H command code. The command sequence is shown in followed Figure 15. If the "Continuous Read Mode" bits (M5-4) do not equal to (1, 0), the next command requires the first E7H command code, thus returning to normal operation. A "Continuous Read Mode" Reset command can be used to reset (M5-4) before issuing normal command.

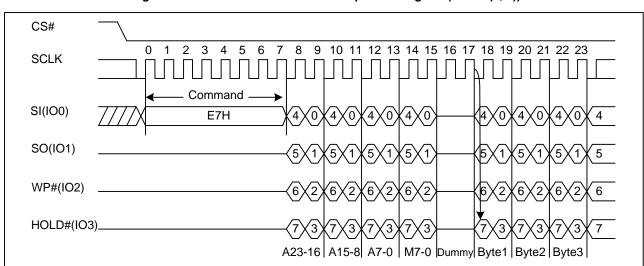


Figure15. Quad I/O Word Fast Read Sequence Diagram (M5-4≠ (1, 0))

Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.

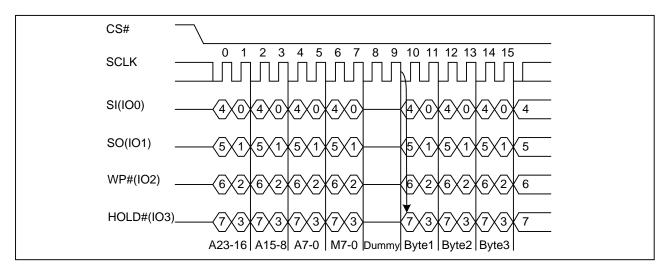


Figure15a. Quad I/O Word Fast Read Sequence Diagram (M5-4= (1, 0))

Quad I/O Word Fast Read with "8/16/32/64-Byte Wrap Around" in Standard SPI mode

The Quad I/O Word Fast Read command can be used to access a specific portion within a page by issuing "Set Burst with Wrap" (77H) commands prior to E7H. The "Set Burst with Wrap" (77H) command can either enable or disable the "Wrap Around" feature for the following E7H commands. When "Wrap Around" is enabled, the data being accessed can be limited to either an 8/16/32/64-byte section of a 256-byte page. The output data starts at the initial address specified in the command, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around the beginning boundary automatically until CS# is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing multiple read commands. The "Set Burst with Wrap" command allows three "Wrap Bits" W6-W4 to be set. The W4 bit is used to enable or disable the "Wrap Around" operation while W6-W5 is used to specify the length of the wrap around section within a page.

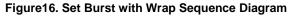
7.15. Set Burst with Wrap (77H)

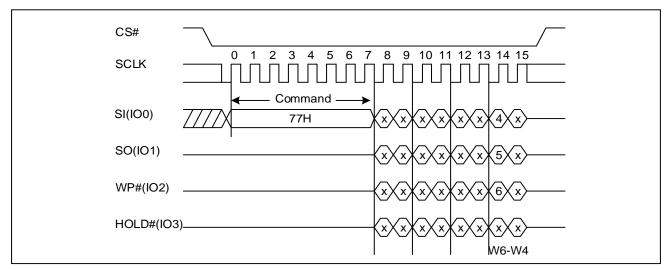
The Set Burst with Wrap command is used in conjunction with "Quad I/O Fast Read" and "Quad I/O Word Fast Read" command to access a fixed length of 8/16/32/64-byte section within a 256-byte page, in standard SPI mode.

The Set Burst with Wrap command sequence: CS# goes low \rightarrow Send Set Burst with Wrap command \rightarrow Send 24 dummy bits \rightarrow Send 8 bits "Wrap bits" \rightarrow CS# goes high.

W6,W5	W 4	l=0	W4=1 (default)		
	Wrap Around	Wrap Length	Wrap Around	Wrap Length	
0, 0	Yes	8-byte	No	N/A	
0, 1	Yes	16-byte	No	N/A	
1, 0	Yes	32-byte	No	N/A	
1, 1	Yes	64-byte	No	N/A	

If the W6-W4 bits are set by the Set Burst with Wrap command, all the following "Quad I/O Fast Read" and "Quad I/O Word Fast Read" command will use the W6-W4 setting to access the 8/16/32/64-byte section within any page. To exit the "Wrap Around" function and return to normal read operation, another Set Burst with Wrap command should be issued to set W4=1. In QPI mode, the "Burst Read with Wrap (0CH)" command should be used to perform the Read Operation with "Wrap Around" feature. The Wrap Length set by W5-W6 in Standard SPI mode is still valid in QPI mode and can also be re-configured by "Set Read Parameters (C0H) command.





Page Program (PP) (02H) 7.16.

The Page Program (PP) command is for programming the memory. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit before sending the Page Program command.

The Page Program (PP) command is entered by driving CS# Low, followed by the command code, three address bytes and at least one data byte on SI. If the 8 least significant address bits (A7-A0) are not all zero, all transmitted data that goes beyond the end of the current page are programmed from the start address of the same page (from the address whose 8 least significant bits (A7-A0) are all zero). CS# must be driven low for the entire duration of the sequence. The Page Program command sequence: CS# goes low \rightarrow sending Page Program command \rightarrow 3-byte address or 4-byte address on SI \rightarrow at least 1 byte data on SI \rightarrow CS# goes high. The command sequence is shown in Figure 17. If more than 256 bytes are sent to the device, previously latched data are discarded and the last 256 data bytes are guaranteed to be programmed correctly within the same page. If less than 256 data bytes are sent to device, they are correctly programmed at the requested addresses without having any effects on the other bytes of the same page. CS# must be driven high after the eighth bit of the last data byte has been latched in; otherwise the Page Program (PP) command is not executed.

As soon as CS# is driven high, the self-timed Page Program cycle (whose duration is tPP) is initiated. While the Page Program cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Page Program cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset.

A Page Program (PP) command applied to a page which is protected by the Block Protect (BP4, BP3, BP2, BP1, and BP0) is not executed.

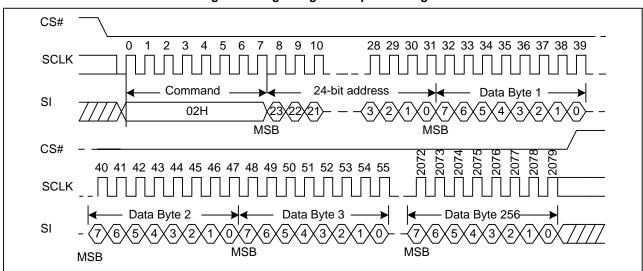
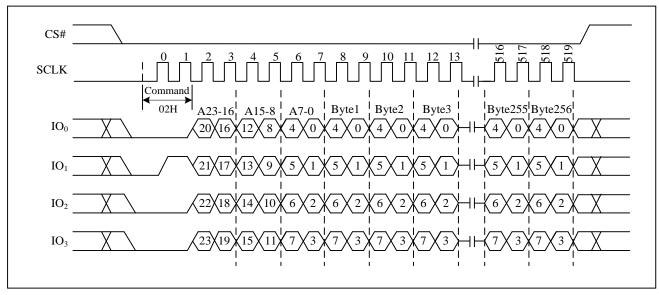


Figure17. Page Program Sequence Diagram



GD25LQ256C





7.17. Quad Page Program (32H)

The Quad Page Program command is for programming the memory using four pins: IO0, IO1, IO2, and IO3. To use Quad Page Program the Quad enable in status register Bit9 must be set (QE=1). A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit before sending the Page Program command. The quad Page Program command is entered by driving CS# Low, followed by the command code (32H), three or four address bytes and at least one data byte on IO pins.

The command sequence is shown in Figure 18. If more than 256 bytes are sent to the device, previously latched data are discarded and the last 256 data bytes are guaranteed to be programmed correctly within the same page. If less than 256 data bytes are sent to device, they are correctly programmed at the requested addresses without having any effects on the other bytes of the same page. CS# must be driven high after the eighth bit of the last data byte has been latched in; otherwise the Quad Page Program (PP) command is not executed.

As soon as CS# is driven high, the self-timed Quad Page Program cycle (whose duration is tPP) is initiated. While the Quad Page Program cycle is in progress, the Status Register may be read to check the value of the Write In Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Quad Page Program cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset.

A Quad Page Program command applied to a page which is protected by the Block Protect (BP4, BP3, BP2, BP1, and BP0) is not executed.

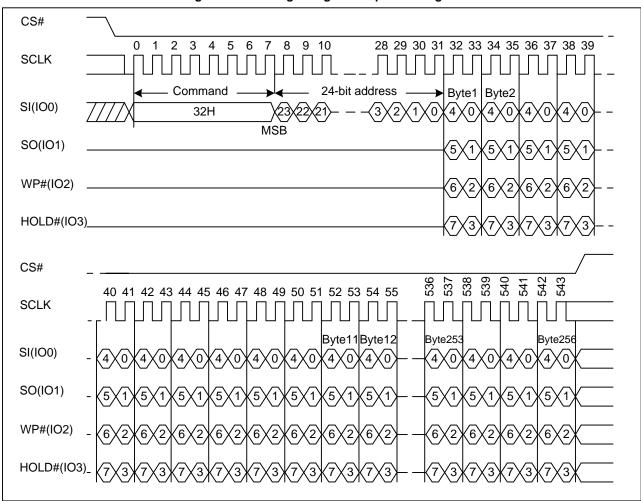


Figure18.Quad Page Program Sequence Diagram

Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.

Sector Erase (SE) (20H) 7.18.

The Sector Erase (SE) command is erased the all data of the chosen sector. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit. The Sector Erase (SE) command is entered by driving CS# low, followed by the command code, and 3- byte address or 4-byte address on SI. Any address inside the sector is a valid address for the Sector Erase (SE) command. CS# must be driven low for the entire duration of the sequence.

The Sector Erase command sequence: CS# goes low \rightarrow sending Sector Erase command \rightarrow 3-byte address or 4-byte address on SI → CS# goes high. The command sequence is shown in Figure 19. CS# must be driven high after the eighth bit of the last address byte has been latched in; otherwise the Sector Erase (SE) command is not executed. As soon as CS# is driven high, the self-timed Sector Erase cycle (whose duration is tsE) is initiated. While the Sector Erase cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Sector Erase cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset. A Sector Erase (SE) command applied to a sector which is protected by the Block Protect (BP4, BP3, BP2, BP1, and BP0) bit (see Table1&1a) is not executed.

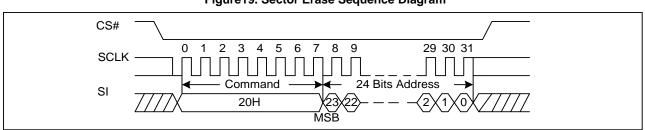


Figure19. Sector Erase Sequence Diagram

Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.

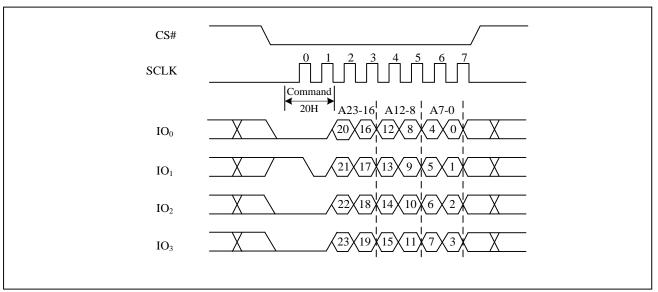


Figure19a. Sector Erase Sequence Diagram (QPI)

1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash 7.19. 32KB Block Erase (BE) (52H)

The 32KB Block Erase (BE) command is erased the all data of the chosen block. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit. The 32KB Block Erase (BE) command is entered by driving CS# low, followed by the command code, and 3-byte address or 4-byte address on SI. Any address inside the block is a valid address for the 32KB Block Erase (BE) command. CS# must be driven low for the entire duration of the sequence.

The 32KB Block Erase command sequence: CS# goes low \rightarrow sending 32KB Block Erase command \rightarrow 3-byte address or 4-byte address on SI → CS# goes high. The command sequence is shown in Figure20. CS# must be driven high after the eighth bit of the last address byte has been latched in; otherwise the 32KB Block Erase (BE) command is not executed. As soon as CS# is driven high, the self-timed Block Erase cycle (whose duration is tsE) is initiated. While the Block Erase cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Block Erase cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset. A 32KB Block Erase (BE) command applied to a block which is protected by the Block Protect (BP4, BP3, BP2, BP1, and BP0) bits (see Table1&1a) is not executed.

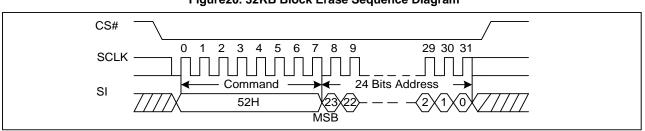


Figure20. 32KB Block Erase Sequence Diagram

Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.

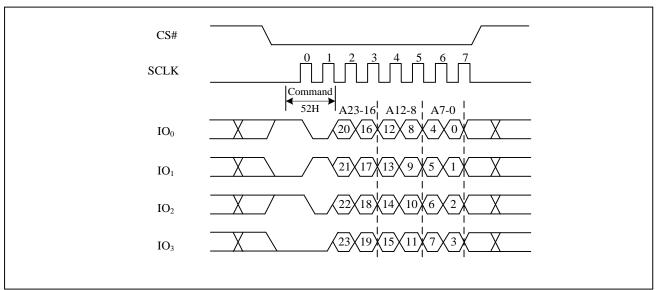
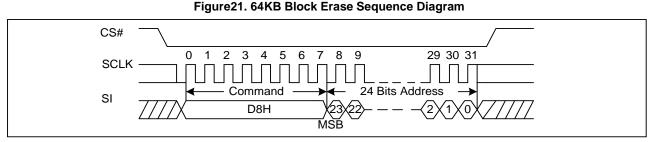


Figure20a. 32KB Block Erase Sequence Diagram (QPI)

1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash 7.20. 64KB Block Erase (BE) (D8H)

The 64KB Block Erase (BE) command is erased the all data of the chosen block. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit. The 64KB Block Erase (BE) command is entered by driving CS# low, followed by the command code, and 3-byte address or 4-byte address on SI. Any address inside the block is a valid address for the 64KB Block Erase (BE) command. CS# must be driven low for the entire duration of the sequence.

The 64KB Block Erase command sequence: CS# goes low \rightarrow sending 64KB Block Erase command \rightarrow 3-byte address or 4-byte address on SI \rightarrow CS# goes high. The command sequence is shown in Figure21. CS# must be driven high after the eighth bit of the last address byte has been latched in; otherwise the 64KB Block Erase (BE) command is not executed. As soon as CS# is driven high, the self-timed Block Erase cycle (whose duration is t_{SE}) is initiated. While the Block Erase cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Block Erase cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset. A 64KB Block Erase (BE) command applied to a block which is protected by the Block Protect (BP4, BP3, BP2, BP1, and BP0) bits (see Table1&1a) is not executed.



Note: The device default is in 24-bit address mode. For 4-byte mode, the address length becomes 32-bit.

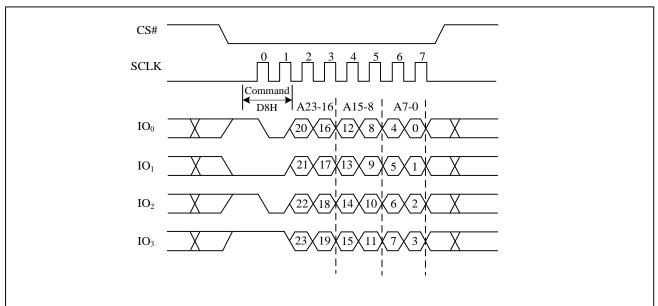


Figure21a. 64KB Block Erase Sequence Diagram (QPI)

1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash 7.21. Chip Erase (CE) (60/C7H)

The Chip Erase (CE) command is erased the all data of the chip. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit .The Chip Erase (CE) command is entered by driving CS# Low, followed by the command code on Serial Data Input (SI). CS# must be driven Low for the entire duration of the sequence.

The Chip Erase command sequence: CS# goes low \rightarrow sending Chip Erase command \rightarrow CS# goes high. The command sequence is shown in Figure22. CS# must be driven high after the eighth bit of the command code has been latched in; otherwise the Chip Erase command is not executed. As soon as CS# is driven high, the self-timed Chip Erase cycle (whose duration is t_{CE}) is initiated. While the Chip Erase cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Chip Erase cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset. The Chip Erase (CE) command is executed only if all Block Protect (BP2, BP1, and BP0) bits are 0. The Chip Erase (CE) command is gnored if one or more sectors are protected.

Figure22. Chip Erase Sequence Diagram

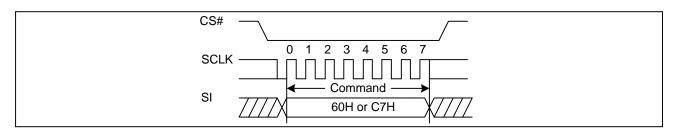
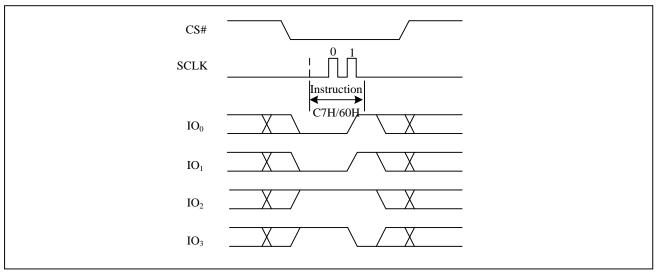


Figure22a. Chip Erase Sequence Diagram (QPI)



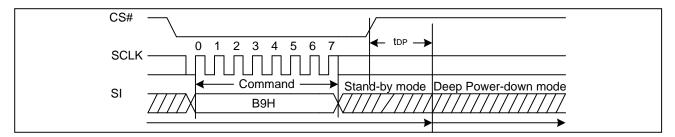
Deep Power-Down (DP) (B9H) 7.22.

Executing the Deep Power-Down (DP) command is the only way to put the device in the lowest consumption mode (the Deep Power-Down Mode). It can also be used as an extra software protection mechanism, while the device is not in active use, since in this mode, the device ignores all Write, Program and Erase commands. Driving CS# high deselects the device, and puts the device in the Standby Mode (if there is no internal cycle currently in progress). But this mode is not the Deep Power-Down Mode. The Deep Power-Down Mode can only be entered by executing the Deep Power-Down (DP) command. Once the device has entered the Deep Power-Down Mode, all commands are ignored except the Release from Deep Power-Down and Read Device ID (RDI) command. This releases the device from this mode. The Release from Deep Power-Down and Read Device ID (RDI) command also allows the Device ID of the device to be output on SO.

The Deep Power-Down Mode automatically stops at Power-Down, and the device always Power-Up in the Standby Mode. The Deep Power-Down (DP) command is entered by driving CS# low, followed by the command code on SI. CS# must be driven low for the entire duration of the sequence.

The Deep Power-Down command sequence: CS# goes low \rightarrow sending Deep Power-Down command \rightarrow CS# goes high. The command sequence is shown in Figure 23. CS# must be driven high after the eighth bit of the command code has been latched in; otherwise the Deep Power-Down (DP) command is not executed. As soon as CS# is driven high, it requires a delay of top before the supply current is reduced to Icc2 and the Deep Power-Down Mode is entered. Any Deep Power-Down (DP) command, while an Erase, Program or Write cycle is in progress, is rejected without having any effects on the cycle that is in progress.





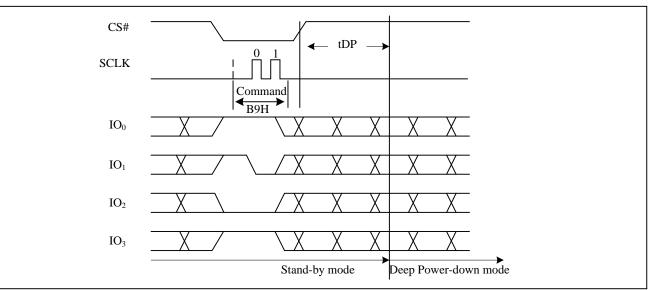


Figure23a. Deep Power-Down Sequence Diagram (QPI)

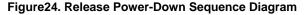
7.23. Release from Deep Power-Down and Read Device ID (RDI) (ABH)

The Release from Power-Down and Read Device ID command is a multi-purpose command. It can be used to release the device from the Power-Down state or obtain the devices electronic identification (ID) number.

To release the device from the Power-Down state, the command is issued by driving the CS# pin low, shifting the instruction code "ABH" and driving CS# high as shown in Figure24. Release from Power-Down will take the time duration of t_{RES1} (See AC Characteristics) before the device will resume normal operation and other command are accepted. The CS# pin must remain high during the t_{RES1} time duration.

When used only to obtain the Device ID while not in the Power-Down state, the command is initiated by driving the CS# pin low and shifting the instruction code "ABH" followed by 3-dummy byte. The Device ID bits are then shifted out on the falling edge of SCLK with most significant bit (MSB) first as shown in Figure24. The Device ID value for the GD25LQ256C is listed in Manufacturer and Device Identification table. The Device ID can be read continuously. The command is completed by driving CS# high.

When used to release the device from the Power-Down state and obtain the Device ID, the command is the same as previously described, and shown in Figure25, except that after CS# is driven high it must remain high for a time duration of t_{RES2} (See AC Characteristics). After this time duration the device will resume normal operation and other command will be accepted. If the Release from Power-Down / Device ID command is issued while an Erase, Program or Write cycle is in process (when WIP equal 1) the command is ignored and will not have any effects on the current cycle.



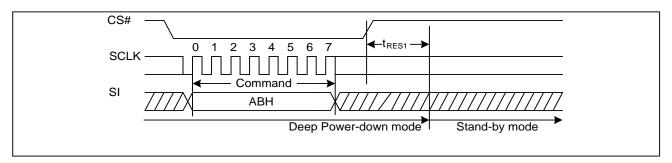
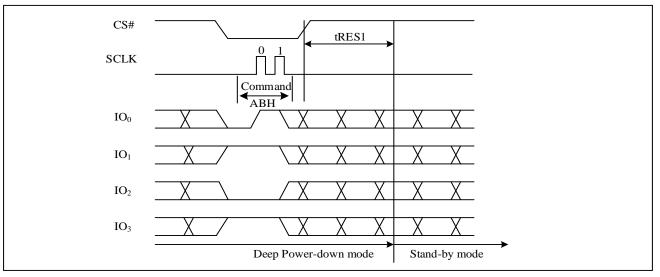


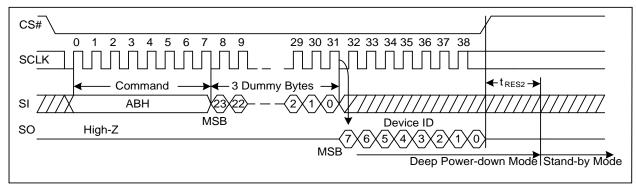
Figure24a. Release Power-Down Sequence Diagram (QPI)

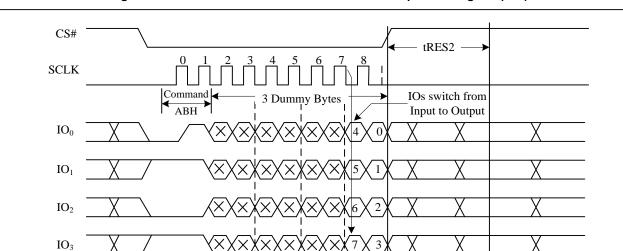


GD25LQ256C

Stand-by mode

Figure25. Release Power-Down/Read Device ID Sequence Diagram





Device ID

Deep Power-down mode

Figure25a. Release Power-Down/Read Device ID Sequence Diagram (QPI)

1.8V Uniform Sector

7.24. Read Manufacture ID/ Device ID (REMS) (90H)

The Read Manufacturer/Device ID command is an alternative to the Release from Power-Down / Device ID command that provides both the JEDEC assigned Manufacturer ID and the specific Device ID.

The command is initiated by driving the CS# pin low and shifting the command code "90H" followed by a 24-bit address (A23-A0) of 000000H. After which, the Manufacturer ID and the Device ID are shifted out on the falling edge of SCLK with most significant bit (MSB) first as shown in Figure26. If the 24-bit address is initially set to 000001H, the Device ID will be read first.

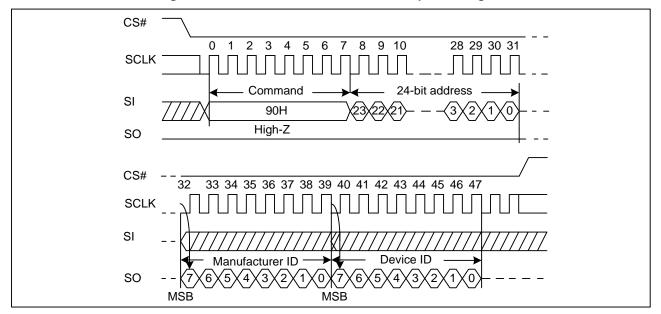
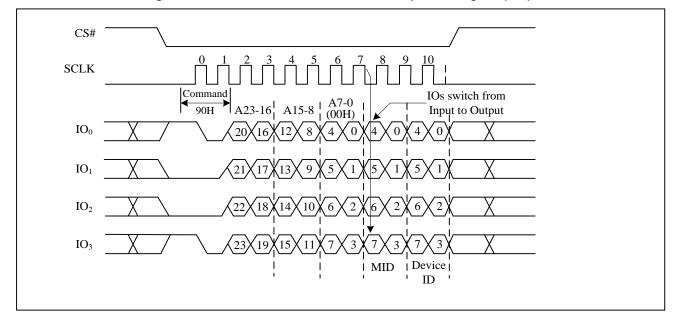


Figure26. Read Manufacture ID/ Device ID Sequence Diagram

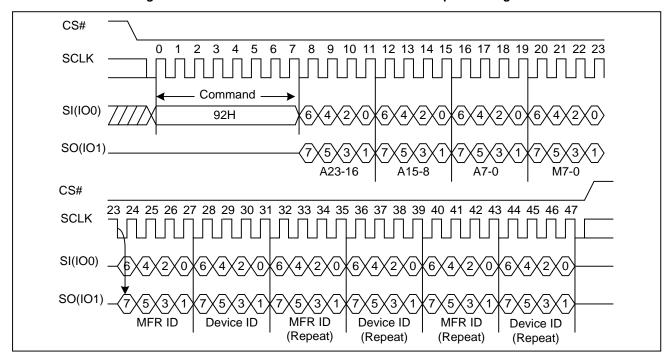
Figure26a. Read Manufacture ID/ Device ID Sequence Diagram (QPI)



7.25. Read Manufacture ID/ Device ID Dual I/O (92H)

The Read Manufacturer/Device ID Dual I/O command is an alternative to the Release from Power-Down / Device ID command that provides both the JEDEC assigned Manufacturer ID and the specific Device ID by dual I/O.

The command is initiated by driving the CS# pin low and shifting the command code "92H" followed by a 24-bit address (A23-A0) of 000000H. After which, the Manufacturer ID and the Device ID are shifted out on the falling edge of SCLK with most significant bit (MSB) first as shown in Figure27. If the 24-bit address is initially set to 000001H, the Device ID will be read first.





7.26. Read Manufacture ID/ Device ID Quad I/O (94H)

The Read Manufacturer/Device ID Quad I/O command is an alternative to the Release from Power-Down / Device ID command that provides both the JEDEC assigned Manufacturer ID and the specific Device ID by quad I/O.

The command is initiated by driving the CS# pin low and shifting the command code "94H" followed by a 24-bit address (A23-A0) of 000000H. After which, the Manufacturer ID and the Device ID are shifted out on the falling edge of SCLK with most significant bit (MSB) first as shown in Figure 28. If the 24-bit address is initially set to 000001H, the Device ID will be read first.

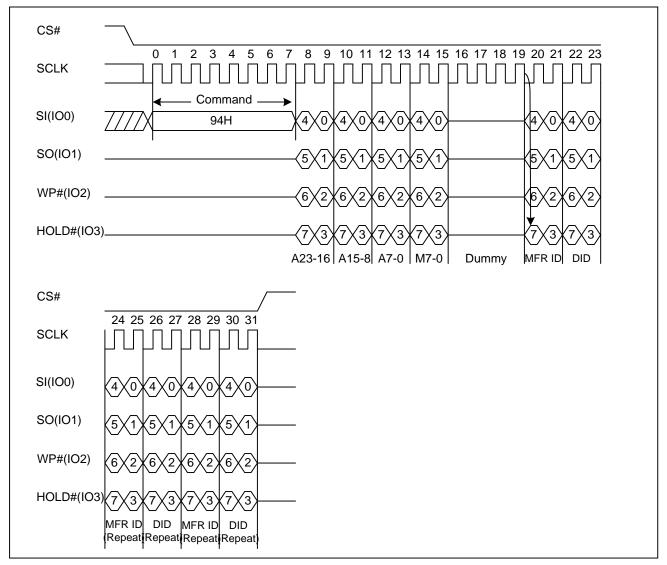


Figure 28. Read Manufacture ID/ Device ID Quad I/O Sequence Diagram

1.8V Uniform Sector <u>GigaDevice</u> Dual and Quad Serial Flash 7.27. Read Identification (RDID) (9FH)

The Read Identification (RDID) command allows the 8-bit manufacturer identification to be read, followed by two bytes of device identification. The device identification indicates the memory type in the first byte, and the memory capacity of the device in the second byte. The Read Identification (RDID) command while an Erase or Program cycle is in progress, is not decoded, and has no effect on the cycle that is in progress. The Read Identification (RDID) command should not be issued while the device is in Deep Power-Down Mode.

The device is first selected by driving CS# to low. Then, the 8-bit command code for the command is shifted in. This is followed by the 24-bit device identification, stored in the memory, being shifted out on Serial Data Output, each bit being shifted out during the falling edge of Serial Clock. The command sequence is shown in Figure 29. The Read Identification (RDID) command is terminated by driving CS# to high at any time during data output. When CS# is driven high, the device is put in the Standby Mode. Once in the Standby Mode, the device waits to be selected, so that it can receive, decode and execute commands.

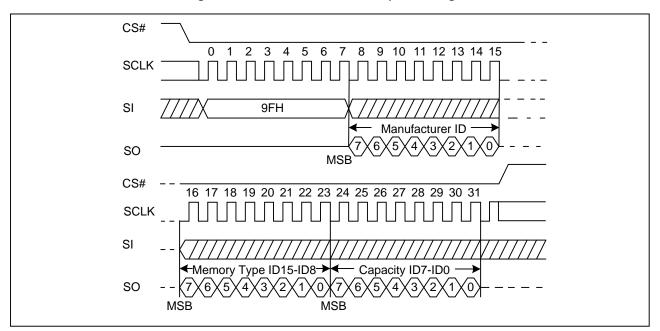
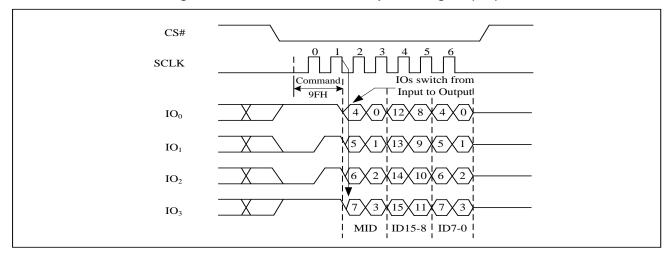


Figure29. Read Identification ID Sequence Diagram

Figure29a. Read Identification ID Sequence Diagram (QPI)



1.8V Uniform Sector <u>GigaDevice</u> Dual and Quad Serial Flash 7.28. Program/Erase Suspend (PES) (75H)

The Program/Erase Suspend command "75H", allows the system to interrupt a page program or sector/block erase operation and then read data from any other sector or block. The Write Status Register command (01H) and Erase Security Registers (44H, 42H) and Erase commands (20H, 52H, D8H, C7H, 60H) and Page Program command are not allowed during Program/Erase suspend. Program/Erase Suspend is valid only during the page program or sector/block erase operation. A maximum of time of "tsus" (See AC Characteristics) is required to suspend the program/erase operation.

The Program/Erase Suspend command will be accepted by the device only if the SUS2/SUS1 bit in the Status Register equal to 0 and WIP bit equal to 1 while a Page Program or a Sector or Block Erase operation is on-going. If the SUS2/SUS1 bit equal to 1 or WIP bit equal to 0, the Suspend command will be ignored by the device. The WIP bit will be cleared from 1 to 0 within "tsus" and the SUS2/SUS1 bit will be set from 0 to 1 immediately after Program/Erase Suspend. A power-off during the suspend period will reset the device and release the suspend state. The command sequence is show in Figure30.

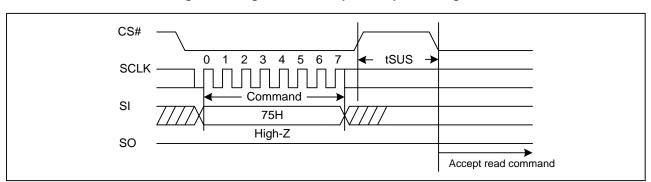
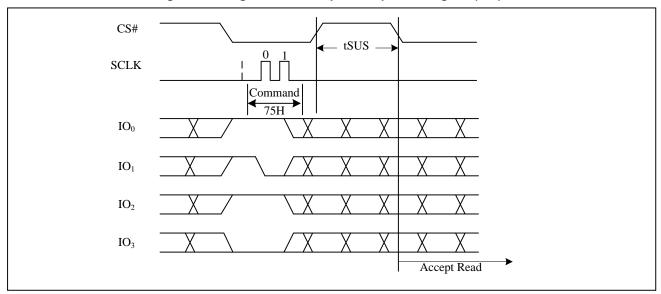


Figure 30. Program/Erase Suspend Sequence Diagram

Figure30a. Program/Erase Suspend Sequence Diagram (QPI)



1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash Program/Erase Resume (PER) (7AH) 7.29.

The Program/Erase Resume command must be written to resume the program or sector/block erase operation after a Program/Erase Suspend command. The Program/Erase command will be accepted by the device only if the SUS2/SUS1 bit equal to 1 and the WIP bit equal to 0. After issued the SUS2/SUS1 bit in the status register will be cleared from 1 to 0 immediately, the WIP bit will be set from 0 to 1 within 200ns and the Sector or Block will complete the erase operation or the page will complete the program operation. The Program/Erase Resume command will be ignored unless a Program/Erase Suspend is active. The command sequence is show in Figure 31.

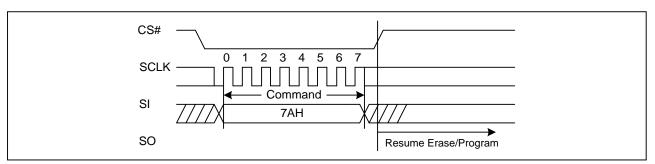
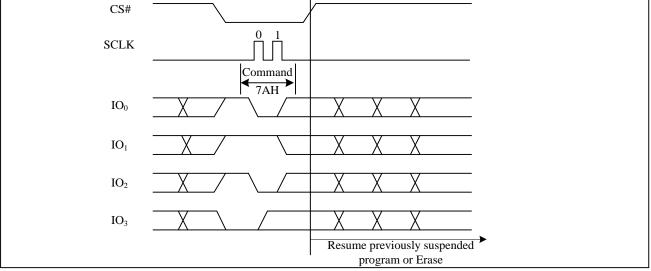


Figure31. Program/Erase Resume Sequence Diagram



Figure31a. Program/Erase Resume Sequence Diagram (QPI)



1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash 7.30 Eraso Socurity Pagistors (44H)

7.30. Erase Security Registers (44H)

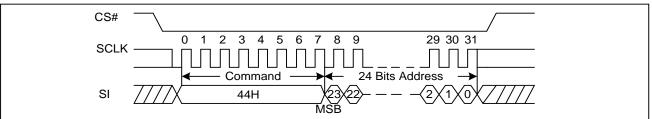
The GD25LQ256C provides two 512-byte Security Registers which can be erased and programmed individually. These registers may be used by the system manufacturers to store security and other important information separately from the main memory array.

The Erase Security Registers command is similar to Sector/Block Erase command. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit.

The Erase Security Registers command sequence: CS# goes low \rightarrow sending Erase Security Registers command \rightarrow CS# goes high. The command sequence is shown in Figure32. CS# must be driven high after the eighth bit of the command code has been latched in; otherwise the Erase Security Registers command is not executed. As soon as CS# is driven high, the self-timed Erase Security Registers cycle (whose duration is tse) is initiated. While the Erase Security Registers cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Erase Security Registers cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset. The Security Registers Lock Bit (LB2-3) in the Status Register can be used to OTP protect the security registers. Once the LB bit is set to 1, the Security Registers will be permanently locked; the Erase Security Registers command will be ignored.

Address	A23-16	A15-12	A11-9	A8-0
Security Register #2	00H	0010	000	Don't care
Security Register #3	00H	0011	000	Don't care





1.8V Uniform Sector <u>GigaDevice</u> Dual and Quad Serial Flash 7.31. Program Security Registers (42H)

The Program Security Registers command is similar to the Page Program command. It allows from 1 to 512 bytes Security Registers data to be programmed. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit before sending the Program Security Registers command. The Program Security Registers command is entered by driving CS# Low, followed by the command code (42H), three address bytes and at least one data byte on SI. As soon as CS# is driven high, the self-timed Program Security Registers cycle (whose duration is t_{PP}) is initiated. While the Program Security Registers cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Program Security Registers cycle, and is 0 when it is completed. At some unspecified time before the cycle is completed, the Write Enable Latch (WEL) bit is reset.

If the Security Registers Lock Bit (LB2-3) is set to 1, the Security Registers will be permanently locked. Program Security Registers command will be ignored.

Address	A23-16	A15-12	A11-9	A8-0
Security Register #2	00H	0010	000	Byte Address
Security Register #3	00H	0011	000	Byte Address

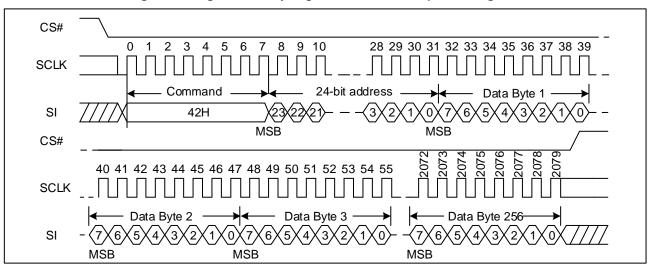


Figure33. Program Security Registers command Sequence Diagram

1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash 7.32 Pood Socurity Projectors (48H)

7.32. Read Security Registers (48H)

The Read Security Registers command is similar to Fast Read command. The command i is followed by a 3-byte address (A23-A0) and a dummy byte, each bit being latched-in during the rising edge of SCLK. Then the memory content, at that address, is shifted out on SO, each bit being shifted out, at a Max frequency fc, during the falling edge of SCLK. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. Once the A8-A0 address reaches the last byte of the register (Byte 1FFH), it will reset to 000H, the command is completed by driving CS# high.

Address	A23-16	A15-12	A11-9	A8-0
Security Register #2	00H	0010	000	Byte Address
Security Register #3	00H	0011	000	Byte Address

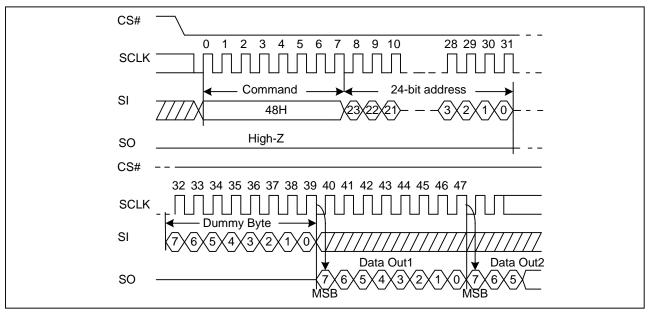


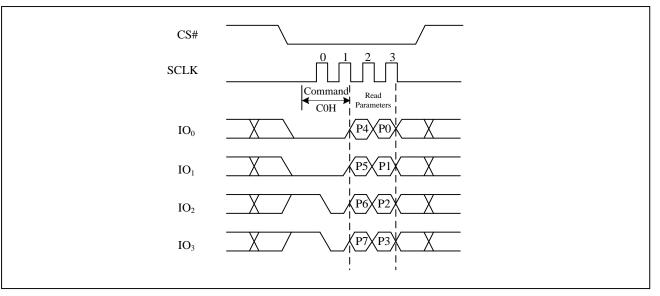
Figure34. Read Security Registers command Sequence Diagram

7.33. Set Read Parameters (C0H)

In QPI mode the "Set Read Parameters (C0H)" command can be used to configure the number of dummy clocks for "Fast Read (0BH)", "Quad I/O Fast Read (EBH)", "Burst Read with Wrap (0CH)", "Burst Read with Wrap for Lower 128Mb (8CH)" and "Burst Read with Wrap For Higher 128Mb (8DH)" command, and to configure the number of bytes of "Wrap Length" for the "Burst Read with Wrap (0CH)" command. The "Wrap Length" is set by W5-6 bit in the "Set Burst with Wrap (77H)" command. This setting will remain unchanged when the device is switched from Standard SPI mode to QPI mode.

P5-P4	Dummy Clocks	Maximum Read Freq.	P1-P0	Wrap Length
0 0	4	80MHz	0 0	8-byte
0 1	6	108MHz	0 1	16-byte
10	8	120MHz	1 0	32-byte
11	8	120MHz	11	64-byte

Figure35. Set Read Parameters command Sequence Diagram



Burst Read with Wrap (0CH) 7.34.

The "Burst Read with Wrap (0CH)" command provides an alternative way to perform the read operation with "Wrap Around" in QPI mode. This command is similar to the "Fast Read (0BH)" command in QPI mode, except the addressing of the read operation will "Wrap Around" to the beginning boundary of the "Wrap Around" once the ending boundary is reached. The "Wrap Length" and the number of dummy clocks can be configured by the "Set Read Parameters (COH)" command.

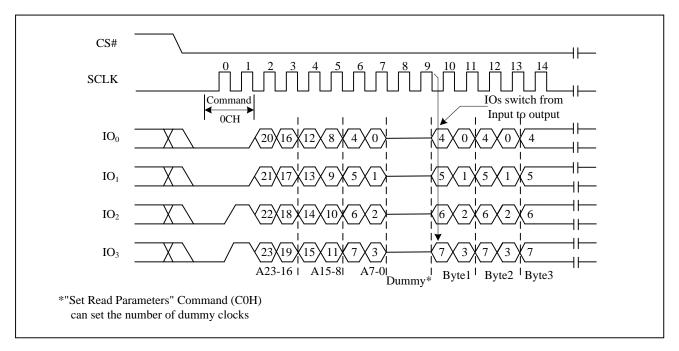


Figure36. Burst Read with Wrap command Sequence Diagram

1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash 7.25 Burst Boad with Wrap for Lower 128Mb (8CH)

7.35. Burst Read with Wrap for Lower 128Mb (8CH)

The "Burst Read with Wrap for Lower 128Mb (8CH)" command provides an alternative way to perform the read operation with "Wrap Around" in QPI mode. This command is similar to the "Fast Read (0BH)" command in QPI mode, except the addressing of the read operation will "Wrap Around" to the beginning boundary of the "Wrap Around" once the ending boundary is reached. The "Wrap Length" and the number of dummy clocks can be configured by the "Set Read Parameters (C0H)" command. The "Burst Read with Wrap for Lower 128Mb (8CH)" command will read out the memory content from 000000H to 0FFFFFH.

The "Burst Read with Wrap for Lower 128Mb (8CH)" command sequence: CS# goes low \rightarrow sending The "Burst Read with Wrap for Lower 128Mb (8CH)" command \rightarrow sending 3-byte address (A23-A0, The A24 default value is 0) \rightarrow sending dummy byte \rightarrow then data out.

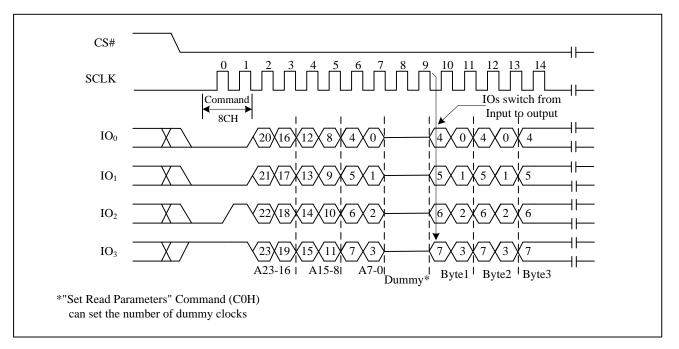


Figure37. Burst Read with Wrap for Lower 128Mb command Sequence Diagram

1.8V Uniform Sector GigaDevice Dual and Quad Serial Flash 7.26 Buret Boad with Wrop for Higher 428Mb (8DH)

7.36. Burst Read with Wrap for Higher 128Mb (8DH)

The "Burst Read with Wrap for Higher 128Mb (8DH)" command provides an alternative way to perform the read operation with "Wrap Around" in QPI mode. This command is similar to the "Fast Read (0BH)" command in QPI mode, except the addressing of the read operation will "Wrap Around" to the beginning boundary of the "Wrap Around" once the ending boundary is reached. The "Wrap Length" and the number of dummy clocks can be configured by the "Set Read Parameters (C0H)" command. The "Burst Read with Wrap for higher 128Mb (8DH)" command will read out the memory content from 1000000H to 1FFFFFH.

The "Burst Read with Wrap for Higher 128Mb (8DH)" command sequence: CS# goes low \rightarrow sending The "Burst Read with Wrap for Higher 128Mb (8DH)" command \rightarrow sending 3-byte address (A23-A0, The A24 default value is 1) \rightarrow sending dummy byte \rightarrow then data out.

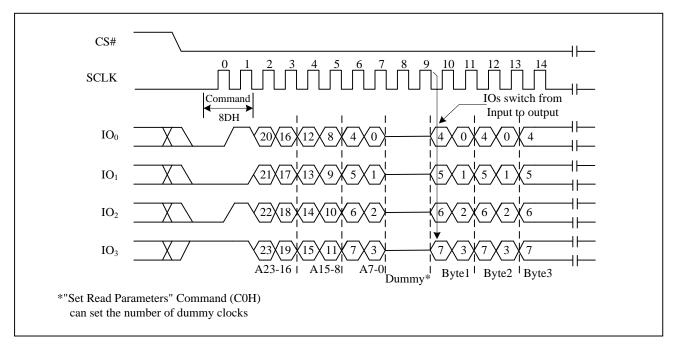
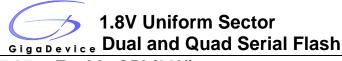


Figure 38. Burst Read with Wrap for Higher 128Mb command Sequence Diagram



7.37. Enable QPI (38H)

The device support both Standard/Dual/Quad SPI and QPI mode. The "Enable QPI (38H)" command can switch the device from SPI mode to QPI mode. See the command Table 2a for all support QPI commands. In order to switch the device to QPI mode, the Quad Enable (QE) bit in Status Register-1 must be set to 1 first, and "Enable QPI (38H)" command must be issued. If the QE bit is 0, the "Enable QPI (38H)" command will be ignored and the device will remain in SPI mode. When the device is switched from SPI mode to QPI mode, the existing Write Enable Latch and Program/Erase Suspend status, and the Wrap Length setting will remain unchanged.

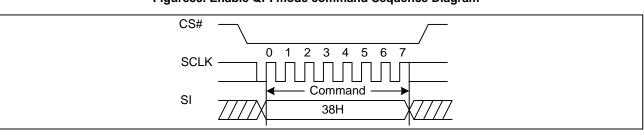
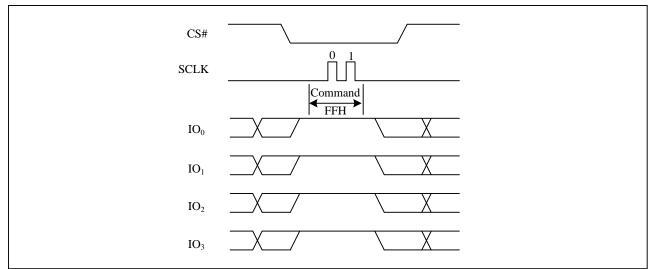


Figure 39. Enable QPI mode command Sequence Diagram

7.38. Disable QPI (FFH)

To exit the QPI mode and return to Standard/Dual/Quad SPI mode, the "Disable QPI (FFH)" command must be issued. When the device is switched from QPI mode to SPI mode, the existing Write Enable Latch and Program/Erase Suspend status, and the Wrap Length setting will remain unchanged.

Figure 40. Disable QPI mode command Sequence Diagram

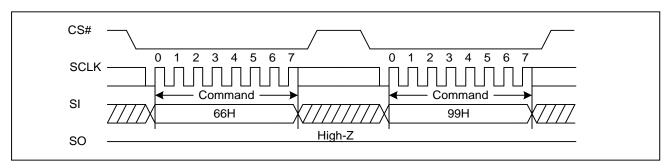


1.8V Uniform Sector <u>GigaDevice</u> Dual and Quad Serial Flash 7.39. Enable Reset (66H) and Reset (99H)

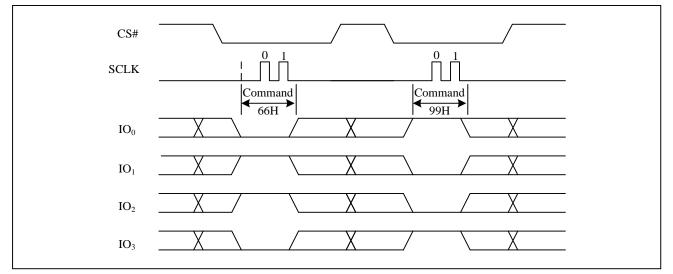
If the Reset command is accepted, any on-going internal operation will be terminated and the device will return to its default power-on state and lose all the current volatile settings, such as Volatile Status Register bits, Write Enable Latch status (WEL), Program/Erase Suspend status, Read Parameter setting (P7-P0), Continuous Read Mode bit setting (M7-M0) and Wrap Bit Setting (W6-W4).

The "Enable Reset (66H)" and the "Reset (99H)" commands can be issued in either SPI or QPI mode. The "Reset (99H)" command sequence as follow: CS# goes low \rightarrow Sending Enable Reset command \rightarrow CS# goes high \rightarrow CS# goes low \rightarrow Sending Reset command \rightarrow CS# goes high. Once the Reset command is accepted by the device, the device will take approximately t_{RST_R} to reset. During this period, no command will be accepted. Data corruption may happen if there is an on-going or suspended internal Erase or Program operation when Reset command sequence is accepted by the device. It is recommended to check the BUSY bit and the SUS bit in Status Register before issuing the Reset command sequence.

Figure 41. Enable Reset and Reset command Sequence Diagram









Read Serial Flash Discoverable Parameter (5AH) 7.40.

The Serial Flash Discoverable Parameter (SFDP) standard provides a consistent method of describing the functional and feature capabilities of serial flash devices in a standard set of internal parameter tables. These parameter tables can be interrogated by host system software to enable adjustments needed to accommodate divergent features from multiple vendors. The concept is similar to the one found in the Introduction of JEDEC Standard, JESD68 on CFI. SFDP is a standard of JEDEC Standard No.216.

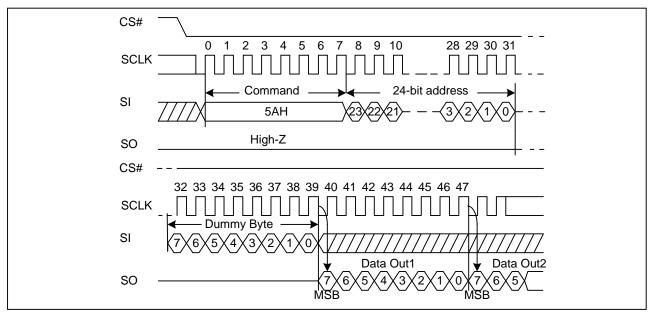
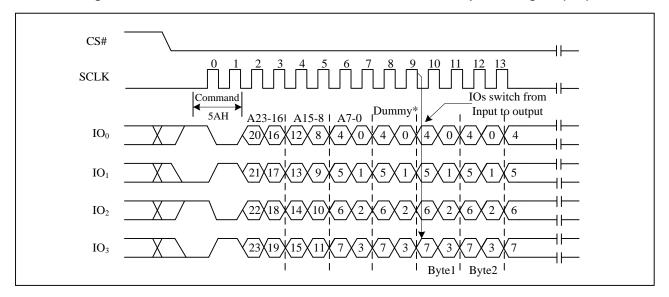




Figure42a. Read Serial Flash Discoverable Parameter command Sequence Diagram (QPI)





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Table3. Signature and Parameter Identification Data Values

Table3. Signature and Parameter Identification Data Values						
Description	Comment	Add(H)	DW Add	Data	Data	
		(Byte)	(Bit)			
SFDP Signature	Fixed:50444653H	00H	07:00	53H	53H	
		01H	15:08	46H	46H	
		02H	23:16	44H	44H	
		03H	31:24	50H	50H	
SFDP Minor Revision Number	Start from 00H	04H	07:00	00H	00H	
SFDP Major Revision Number	Start from 01H	05H	15:08	01H	01H	
Number of Parameters Headers	Start from 00H	06H	23:16	01H	01H	
Unused	Contains 0xFFH and can never be changed	07H	31:24	FFH	FFH	
ID number (JEDEC)	00H: It indicates a JEDEC specified header	08H	07:00	00H	00H	
Parameter Table Minor Revision Number	Start from 0x00H	09H	15:08	00H	00H	
Parameter Table Major Revision Number	Start from 0x01H	0AH	23:16	01H	01H	
Parameter Table Length (in double word)	How many DWORDs in the Parameter table	0BH	31:24	09H	09H	
Parameter Table Pointer (PTP)	First address of JEDEC Flash	0CH	07:00	30H	30H	
	Parameter table	0DH	15:08	00H	00H	
		0EH	23:16	00H	00H	
Unused	Contains 0xFFH and can never be	0FH	31:24	FFH	FFH	
onuseu	changed	UTT	51.24			
ID Number LSB	It is indicates GigaDevice	10H	07:00	C8H	C8H	
(GigaDevice Manufacturer ID)	manufacturer ID					
Parameter Table Minor Revision Number	Start from 0x00H	11H	15:08	00H	00H	
Parameter Table Major Revision Number	Start from 0x01H	12H	23:16	01H	01H	
Parameter Table Length	How many DWORDs in the	13H	31:24	03H	03H	
(in double word)	Parameter table					
Parameter Table Pointer (PTP)	First address of GigaDevice Flash	14H	07:00	60H	60H	
	Parameter table	15H	15:08	00H	00H	
		16H	23:16	00H	00H	
Unused	Contains 0xFFH and can never be changed	17H	31:24	FFH	FFH	
	U					



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Table4. Parameter Table (0): JEDEC Flash Parameter Tables

Description	24. Parameter Table (0): JEDEC Fla Comment	Add(H)	DW Add	Data	Data	
		(Byte)	(Bit)			
	00: Reserved; 01: 4KB erase;					
Block/Sector Erase Size	10: Reserved;		01:00	01b		
	11: not support 4KB erase					
Write Granularity	0: 1Byte, 1: 64Byte or larger		02	1b		
Write Enable Instruction	0. Nonvolotilo ototuo hit		-			
Requested for Writing to	0: Nonvolatile status bit		02	0b		
Volatile	1: Volatile status bit (BP status register bit)		03	du		
Status Registers	(BP status register bit)	30H			E5H	
	0: Use 50H Opcode,					
Write Enable Opcode Select for	1: Use 06H Opcode,					
Writing to Volatile Status	Note: If target flash status register		04	0b		
Registers	is Nonvolatile, then bits 3 and 4					
	must be set to 00b.					
Unused	Contains 111b and can never be		07:05	111b		
	changed		07.00	1110		
4KB Erase Opcode		31H	15:08	20H	20H	
(1-1-2) Fast Read	0=Not support, 1=Support		16	1b		
Address Bytes Number used in	00: 3Byte only, 01: 3 or 4Byte,	-	18:17	01b	F3H	
addressing flash array	10: 4Byte only, 11: Reserved		10.17	0.0		
Double Transfer Rate (DTR)	0=Not support, 1=Support		19	0b		
clocking		32H				
(1-2-2) Fast Read	0=Not support, 1=Support		20	1b	-	
(1-4-4) Fast Read	0=Not support, 1=Support		21	1b		
(1-1-4) Fast Read	0=Not support, 1=Support		22	1b		
Unused			23	1b		
Unused		33H	31:24	FFH	FFH	
Flash Memory Density		37H:34 H	31:00	0FFFF	FFH	
(1-4-4) Fast Read Number of	0 0000b: Wait states (Dummy		04:00	001006		
Wait states	Clocks) not support	2011	04:00	00100b	A A L-1	
(1-4-4) Fast Read Number of	000b:Mode Bits not support	38H	07:05	010b	44H	
Mode Bits			07.05	diub		
(1-4-4) Fast Read Opcode		39H	15:08	EBH	EBH	
(1-1-4) Fast Read Number of	0 0000b: Wait states (Dummy		20.16	010006		
Wait states	Clocks) not support	2411	20:16	01000b	0011	
(1-1-4) Fast Read Number of	000h:Mada Bita pat august	3AH	00.04	0006	08H	
Mode Bits	000b:Mode Bits not support		23:21	000b		
(1-1-4) Fast Read Opcode		3BH	31:24	6BH	6BH	
(1-1-2) Fast Read Number of	0 0000b: Wait states (Dummy	3CH	04:00	01000b	08H	

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Wait states	Clocks) not support				
(1-1-2) Fast Read Number	000b: Mode Bits not support		07:05	000b	
of Mode Bits			07.00	0000	
(1-1-2) Fast Read Opcode		3DH	15:08	3BH	3BH
(1-2-2) Fast Read Number	0 0000b: Wait states (Dummy		20:16	00010b	
of Wait states	Clocks) not support	3EH	20.10	000100	42H
(1-2-2) Fast Read Number	000b: Mode Bits not support	ЗЕП	23:21	010b	4211
of Mode Bits			23.21	0100	
(1-2-2) Fast Read Opcode		3FH	31:24	BBH	BBH
(2-2-2) Fast Read	0=not support 1=support		00	0b	
Unused		4011	03:01	111b	
(4-4-4) Fast Read	0=not support 1=support	40H	04	1b	FEH
Unused			07:05	111b	-
		43H:41			
Unused		н	31:08	0xFFH	0xFFH
		45H:44			
Unused		н	15:00	0xFFH	0xFFH
(2-2-2) Fast Read Number	0 0000b: Wait states (Dummy		00.40	000001	
of Wait states	Clocks) not support	4011	20:16	00000b	0011
(2-2-2) Fast Read Number	000h Mada Dita nat support	46H	00.04	0006	00H
of Mode Bits	000b: Mode Bits not support		23:21	000b	
(2-2-2) Fast Read Opcode		47H	31:24	FFH	FFH
Unused		49H:48	15:00	0xFFH	0xFFH
Unused		Н	15.00	UXEEN	UXFER
(4-4-4) Fast Read Number of	0 0000b: Wait states (Dummy		20:16	00100b	
Wait states	Clocks) not support	4AH	20.10	001000	44H
(4-4-4) Fast Read Number	000b: Mode Bits not support	4/11	23:21	010b	(1)
of Mode Bits			23.21	0100	
(4-4-4) Fast Read Opcode		4BH	31:24	EBH	EBH
Sector Type 1 Size	Sector/block size=2^N bytes	4CH	07:00	0CH	0CH
Sector Type T Size	0x00b: this sector type don't exist	4011	07.00	0011	0011
Sector Type 1 erase Opcode		4DH	15:08	20H	20H
Sector Type 2 Size	Sector/block size=2^N bytes	4EH	22.16	0FH	0FH
Sector Type 2 Size	0x00b: this sector type don't exist	460	23:16	UFH	ULU
Sector Type 2 erase Opcode		4FH	31:24	52H	52H
Sector Type 3 Size	Sector/block size=2^N bytes	50H	07:00	10H	10H
Secior Type 3 Size	0x00b: this sector type don't exist	501	07.00		
Sector Type 3 erase Opcode		51H	15:08	D8H	D8H
Sector Type 4 Size	Sector/block size=2^N bytes	FOLI	22.10	0014	0011
Sector Type 4 Size	0x00b: this sector type don't exist	52H	23:16	00H	00H
Sector Type 4 erase Opcode		53H	31:24	FFH	FFH

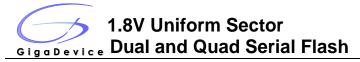


1.8V Uniform Sector Dual and Quad Serial Flash

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Table5. Parameter Table (1):	GigaDevice Flash Parameter Tables
------------------------------	-----------------------------------

Description	Comment	Add(H) (Byte)	DW Add (Bit)	Data	Data
Vcc Supply Maximum Voltage	2000H=2.000∨ 2700H=2.700∨ 3600H=3.600∨	61H:60 H	15:00	2000H	2000H
Vcc Supply Minimum Voltage	1650H=1.650V 2250H=2.250V 2350H=2.350V 2700H=2.700V	63H:62 H	31:16	1650H	1650H
HW Reset# pin	0=not support 1=support		00	0b	
HW Hold# pin	0=not support 1=support		01	1b	
Deep Power Down Mode	0=not support 1=support		02	1b	-
SW Reset	0=not support 1=support		03	1b	
SW Reset Opcode	Should be issue Reset Enable(66H) before Reset cmd.	65H:64 H	11:04	99H	F99EH
Program Suspend/Resume	0=not support 1=support		12	1b	
Erase Suspend/Resume	0=not support 1=support		13	1b	
Unused			14	1b	
Wrap-Around Read mode	0=not support 1=support		15	1b	
Wrap-Around Read mode Opcode		66H	23:16	77H	77H
Wrap-Around Read data length	08H:support 8B wrap-around read 16H:8B&16B 32H:8B&16B&32B 64H:8B&16B&32B&64B	67H	31:24	64H	64H
Individual block lock	0=not support 1=support		00	0b	
Individual block lock bit (Volatile/Nonvolatile)	0=Volatile 1=Nonvolatile		01	0b	
Individual block lock Opcode			09:02	FFH	
Individual block lock Volatile protect bit default protect status	0=protect 1=unprotect	6BH:68	10	0b	EBFC H
Secured OTP	0=not support 1=support	Н	11	1b	
Read Lock	0=not support 1=support		12	0b	
Permanent Lock	0=not support 1=support		13	1b	
Unused			15:14	11b	1
Unused			31:16	FFFFH	FFFFH



8. ELECTRICAL CHARACTERISTICS

8.1. POWER-ON TIMING

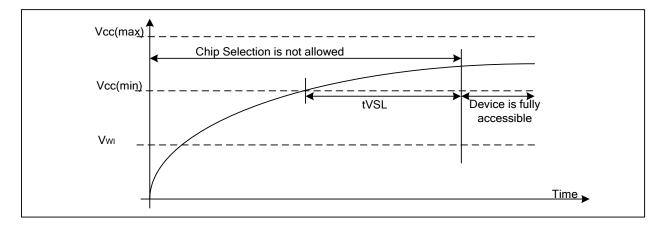


Table6. Power-Up Timing And Write Inhibit Threshold

Symbol	Parameter	Min	Max	Unit
tVSL	VCC(min) To CS# Low	5		ms
VWI	Write Inhibit Voltage VCC(min)	1	1.4	V

8.2. INITIAL DELIVERY STATE

The device is delivered with the memory array erased: all bits are set to 1(each byte contains FFH). The Status Register contains 00H (all Status Register bits are 0).

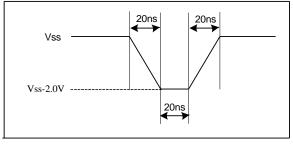
8.3. ABSOLUTE MAXIMUM RATINGS

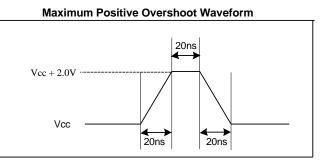
Parameter	Value	Unit
Ambient Operating Temperature	-40 to 85	°C
Storage Temperature	-65 to 150	°C
Transient Input/Output Voltage(note: overshoot)	-2.0 to VCC+2.0	V
Applied Input/Output Voltage	-0.6 to VCC+0.4	V
VCC	-0.6 to 2.5	V

GD25LQ256C

Figure43. Input Test Waveform and Measurement Level

Maximum Negative Overshoot Waveform

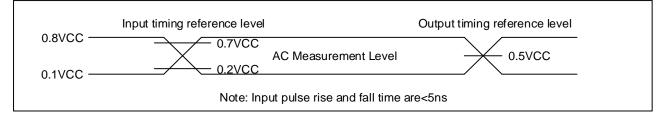




8.4. CAPACITANCE MEASUREMENT CONDITIONS

Symbol	Parameter	Min	Тур	Мах	Unit	Conditions
CIN	Input Capacitance			6	pF	VIN=0V
COUT	Output Capacitance			8	pF	VOUT=0V
CL	Load Capacitance		30		pF	
	Input Rise And Fall time			5	ns	
	Input Pause Voltage	0.2VC	C to 0.8V0	CC	V	
	Input Timing Reference Voltage	0.3VC	0.3VCC to 0.7VCC		V	
	Output Timing Reference Voltage		0.5VCC		V	

Figure44. Input Test Waveform and Measurement Level





1.8V Uniform Sector Dual and Quad Serial Flash

8.5. DC CHARACTERISTICS

(T= -40°C~85°C, VCC=1.65~2.0V)

Symbol	Parameter	Test Condition	Min.	Тур	Max.	Unit.
lu	Input Leakage Current				<u>+2</u>	μA
ILO	Output Leakage Current				±2	μA
Icc1	Standby Current	CS#=VCC,		70	100	μA
		VIN=VCC or VSS				
Icc2	Deep Power-Down Current	CS#=VCC,		2	10	μA
		V _{IN} =VCC or VSS				
		CLK=0.1VCC /				
		0.9VCC		15	20	mA
	Operating Current (Read)	at 120MHz,		15	20	mA
		Q=Open(*1,*2,*4 I/O)				
Іссз		CLK=0.1VCC /				
		0.9VCC		13	10	
		at 80MHz,			18	mA
		Q=Open(*1,*2,*4 I/O)				
Icc4	Operating Current (PP)	CS#=VCC			20	mA
Icc5	Operating Current(WRSR)	CS#=VCC			20	mA
Icc6	Operating Current (SE)	CS#=VCC			20	mA
Icc7	Operating Current (BE)	CS#=VCC			20	mA
VIL	Input Low Voltage		-0.5		0.3VCC	V
VIH	Input High Voltage		0.7VCC		VCC+0.4	V
Vol	Output Low Voltage	I _{OL} =100uA			0.2	V
V _{OH}	Output High Voltage	I _{OH} =-100µА	VCC-0.2			V

Note:

1. Typical values given for TA=25°C.

2. Value guaranteed by design and/or characterization, not 100% tested in production.



8.6. AC CHARACTERISTICS

(T= -40°C~85°C, VCC=1.65~2.0V, CL=30pf)

Symbol	Parameter	Min.	Тур.	Max.	Unit.
Fc	Serial Clock Frequency For: all command except for 03H			120	MHz
f _R	Serial Clock Frequency For: Read (03H)			80	MHz
t CLH	Serial Clock High Time	3.5			ns
tcll	Serial Clock Low Time	3.5			ns
t CLCH	Serial Clock Rise Time (Slew Rate)	0.1			V/ns
t _{CHCL}	Serial Clock Fall Time (Slew Rate)	0.1			V/ns
t slch	CS# Active Setup Time	5			ns
tснян	CS# Active Hold Time	5			ns
t _{SHCH}	CS# Not Active Setup Time	5			ns
tCHSL	CS# Not Active Hold Time	5			ns
tshsl	CS# High Time (read/write)	20			ns
t shqz	Output Disable Time			6	ns
t CLQX	Output Hold Time	1.2			ns
t _{DVCH}	Data In Setup Time	2			ns
tснох	Data In Hold Time	2			ns
t HLCH	Hold# Low Setup Time (relative to Clock)	5			ns
tннсн	Hold# High Setup Time (relative to Clock)	5			ns
tснн∟	Hold# High Hold Time (relative to Clock)	5			ns
tсннн	Hold# Low Hold Time (relative to Clock)	5			ns
t HLQZ	Hold# Low To High-Z Output			6	ns
tннох	Hold# Low To Low-Z Output			6	ns
t _{CLQV}	Clock Low To Output Valid			7	ns
twnsl	Write Protect Setup Time Before CS# Low	20			ns
t SHWL	Write Protect Hold Time After CS# High	100			ns
t _{DP}	CS# High To Deep Power-Down Mode			20	μs
t _{RES1}	CS# High To Standby Mode Without Electronic Signature Read			20	μs
t _{RES2}	CS# High To Standby Mode With Electronic Signature Read			20	μs
tsus	CS# High To Next Command After Suspend			20	us
tw	Write Status Register Cycle Time		5	30	ms
t _{PP}	Page Programming Time		0.7	2.4	ms
tse	Sector Erase Time		90	1000	ms
t _{BE}	Block Erase Time(32K Bytes/64K Bytes)		0.3/0.5	1.2/1.5	S
tCE	Chip Erase Time(GD25LQ256C)		200	400	S
trst_r	CS# High To Next Command After Reset (from read)			20	μs
trst_p	CS# High To Next Command After Reset (from program)			20	μs
trst_e	CS# High To Next Command After Reset (from erase)			12	ms

Note:

1. Typical values given for TA=25°C.

2. Value guaranteed by design and/or characterization, not 100% tested in production.



Figure45. Serial Input Timing

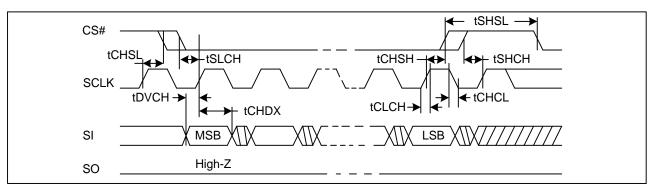


Figure46. Output Timing

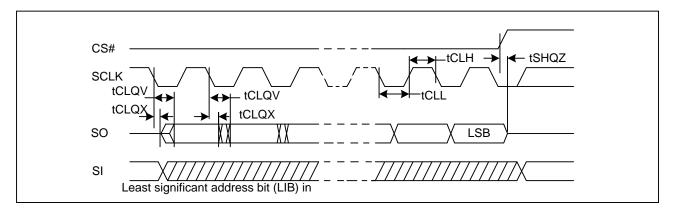
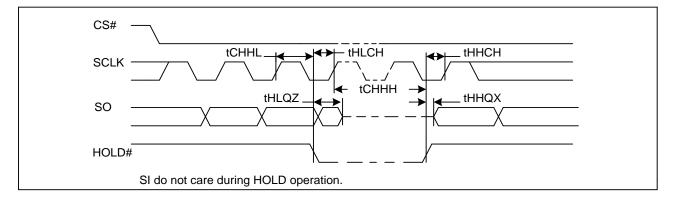


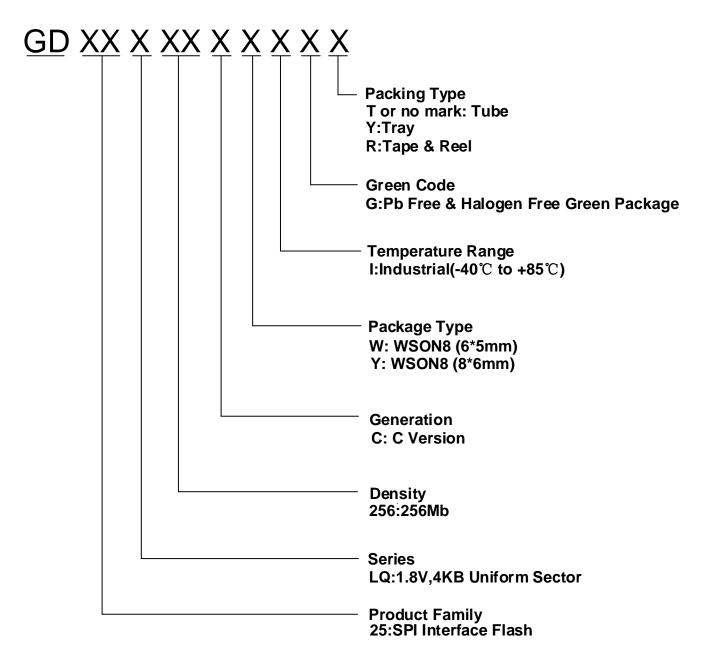
Figure47. Hold Timing





GD25LQ256C

9. ORDERING INFORMATION





1.8V Uniform Sector Dual and Quad Serial Flash

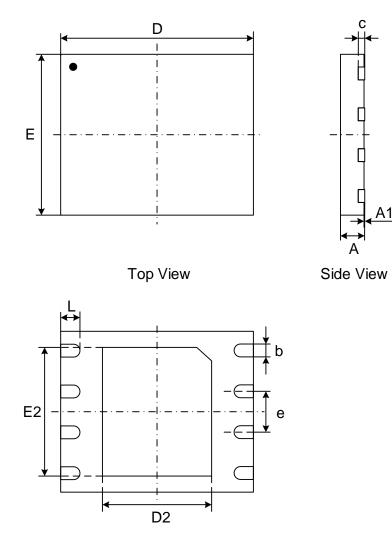
9.1. Valid Part Numbers

Please contact Gigadevice regional sales for the latest product selection and available form factors.

Product Number	Density	Package Type	Temperature
GD25LQ256CWIG	256Mbit	WSON8 (6*5mm)	-40℃ to +85℃
GD25LQ256CYIG	256Mbit	WSON8 (8*6mm)	-40℃ to +85℃

10. PACKAGE INFORMATION

10.1. Package WSON8 (6*5mm)



Bottom View

Dime	nsions										
Syı	mbol	Α	A1	с	b	D	D2	Е	E2	•	
U	Init	~		C	b	D	DZ	E .	E2	e	L
	Min	0.70	0.00	0.180	0.35	5.90	3.30	4.90	3.90		0.50
mm	Nom	0.75	0.02	0.203	0.40	6.00	3.40	5.00	4.00	1.27	0.60
	Max	0.80	0.05	0.250	0.50	6.10	3.50	5.10	4.10		0.75

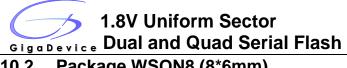
Note:

1. Both the package length and width do not include the mold flash.

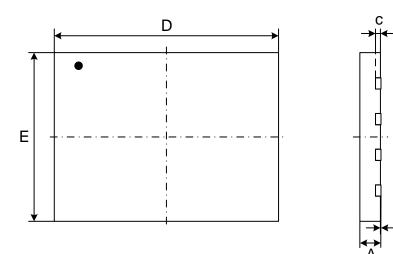
2. The exposed metal pad area on the bottom of the package is floating.

3. Coplanarity ≤ 0.08 mm. Package edge tolerance ≤ 0.10 mm.

4. The lead shape may be of little difference according to different package lead frames. These lead shapes are compatible with each other.



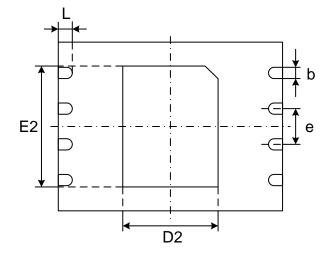
Package WSON8 (8*6mm) 10.2.







A1





Dimensions

Syı	mbol	•	A1		h	6	D2	Е	ES			
U	Init	A	A	AI	С	b	D	DZ	E	E2	e	L
	Min	0.70	0.00	0.180	0.35	7.90	3.30	5.90	4.20		0.45	
mm	Nom	0.75	0.02	0.203	0.40	8.00	3.40	6.00	4.30	1.27	0.50	
	Max	0.80	0.05	0.250	0.45	8.10	3.50	6.10	4.40		0.55	

Note:

1. Both the package length and width do not include the mold flash.

2. The exposed metal pad area on the bottom of the package is floating.

3. Coplanarity ≤ 0.08 mm. Package edge tolerance ≤ 0.10 mm.

4. The lead shape may be of little difference according to different package lead frames. These lead shapes are compatible with each other.

11. REVISION HISTORY

Version No	Description	Page	Date
0.0	Initial Release		2013-9-10
0.1	Update SFDP table		2013-11-4
0.2	Update SFDP table		2013-11-21
	Release to normal version		
	Update AC CHARACTERISTICS: tSE typical 100ms change to		
	90ms		
1.0	Update AC CHARACTERISTICS: tPP typical 1ms change to 0.7ms		2014-3-5
	Update DC CHARACTERISTICS: ICC1 typical 56ms change to		
	70ms		
	Delete Package WSON8 8*6mm		
	Modify Quad SPI mode description		
	Modify Data Protection description		
	Modify BP4, BP3, BP2, BP1, BP0 description		
1.1	Add note on SRP1, SRP0 bits		2014-4-28
	Modify Security Register Address		
	Modify Command Description of 01H, 0BH and EBH		
	Add note on Read SFDP command		
	Update DC CHARACTERISTICS: Icc4, Icc5, Icc6, Icc7 max 10mA		
1.2	change to max 20mA		2014-7-11
1.2	Update DC CHARACTERISTICS: I _{CC3} Test Condition Q=Open(*1		2014-7-11
	I/O) change to Q=Open(*1,*2,*4 I/O)		
1.3	Add Package WSON8 8*6mm		2014-11-17
1.4	Modify Package WSON 8 (6*5mm)		2015-6-18
1.4	Modify Package WSON 8 (8*6mm)	20	
1.5	Modify Serial Clock Frequency		2015-8-10
1.6	Modify AC CHARACTERISTICS: tcll& tclh		2015-9-7
	Modify AC CHARACTERISTICS: tCHCL Min.0.2 V/ns Change to		
1.7	0.1 V/ns		2015-11-11
1.7	tCLCH Min.0.2 V/ns Change to 0.1 V/ns		2013-11-11
	Modify POWER-ON TIMING		
	Add Pin Description Note		
	Modify fc Max.133MHz change to Max.120MHz		
1.8	Modify Power on Timing Diagram		
	Modify tVSL Min.10us change to 5ms		
	Delete tPUW		2016-12-28
	Delete Data Retention and endurance		
	Delete Latch up characteristics		
	Add Transient Input/Output Volatge (note:overshoot):-2.0 to		
	(VCC+2.0)V		

6-5	1.8V Uniform Sector
GigaDevice	Dual and Quad Serial Flash

GD25LQ256C

	Modify VCC:-0.6 to (VCC+0.4)V Change to -0.6 to 2.5V		
	Modify AC CHARACTERISTICS:Add trst_r,trst_p, trst_e		
	Modify Ordering information: Add Valid Part Numbers		
	Modify Figure 43.Input Test Waveform and Measurement Level		
	Figure33. Program Security Registers command Sequence		
	Diagram		
	Modify Package WSON8(8*6mm)		
	Update SFDP		
1.0	Modify Valid Part Numbers		2017.0.4
1.9	Update Package WSON8(6*5mm)		2017-2-4
2.0	Modify tVSL Min.5us change to 5ms		2017-3-24
	Update the description of all packages	P74, 75	0040.0.0
2.1	Add "Page" column to the Revision History	P76, 77	2018-2-8
	Modify the description of EN4B bit (S11)	P12	
2.2	Modify the description of 03H command	P25	2018-11-22
	Modify the table and the sequence diagram of 42H command	P54	
	·		



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